The Reliability Data Program

Expanded Version



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 This reliability report is published by Xilinx to provide insight to our customers concerning the reliability of Xilinx products. Reliability is defined as product performance to specification over time in response to varied (specified) environmental stress. The science of reliability engineering is devoted to improving this product performance through measurement, failure analysis, feedback, and corrective action. The ultimate goal of any reliability program is to achieve continuous improvement in the robustness of the product being evaluated.

As part of this program, finished product reliability is measured periodically to ensure that the product performance meets or exceeds internal and external reliability specifications. Reliability programs are executed in response to internal programs as well as to individual customer requirements. All testing is performed or supervised by experienced Xilinx employees using facilities which are approved and audited by Xilinx for compliance to the requirements of DSCC-VAC and MIL-STD-883 requirements.

- 2. <u>The Reliability Program</u>: The Xilinx reliability qualification of new devices, wafer processes, and packages is designed to ensure that these devices and/or processes satisfy the internal and external customer requirements before transfer into production. The reliability requirements for this transfer are spelled out below.
 - 2.1 New Process/Design Qualification: For new process qualification, the qualifications are to run and pass two wafer lots of high temperature life test. This test accelerates failure mechanisms which are thermally excited by high temperature, such as ionic drift, oxide breakdown, silicon material defects, and assembly related mechanisms. Two lots are run, one to 1,000-hours at 145 degrees C and nominal bias voltage plus 10%. The second lot is run to 168-hours at 145 degrees C and nominal bias voltage plus 10%. The sample size is based on a LTPD = 3.

In addition to the temperature life test, two wafer lots must be run and pass the Bias Moisture life. This evaluates the effectiveness of chip passivation and device packaging. High humidities in the presence of electrical bias promote electro-chemical corrosion, electro-thermal migration, and other chemical reactions involving the presence of water. The required bias moisture life time at Xilinx is 1,000-hours minimum at 85 degrees C temperature, 85% relative humidity and nominal bias voltage. The sample size is based on a LTPD = 3.

One wafer lot must be run and pass the Temperature cycle test. This evaluates the resistance of the die, package combination. The required number of cycles is 500 cycles at -65 degrees C/+150 degrees C. The sample size is based on a LTPD = 3



- 2.2 **Initial Qualification:** For a new die type from a previously qualified process, the requirements are to run one wafer lot of high temperature life test (asa monitor). Lot will be run to 168-hours at 145 degrees C and 5.7 V. or 3.3V. bias; the sample size is based on a LTPD = 3.
- 2.3 **Process Changes:** For major process changes (major changes are identified as outlined per MIL-PRF-38535 Appendix A and MIL-STD-883) that occur to a qualified device, the above requirements (Refer to Section 2.2) are to be again fulfilled.

2.4 New Package Qualification:

2.4.1<u>Non-Hermetic Packages</u>: The non-hermetic package qualification requires one lot to be run for each of the following tests:

Unbiased Pressure Pot - Pressure pot test is performed to identify the effects of high humidity and heat conditions on the die surface. Steam stressing accelerates moisture penetration through the plastic package material to the surface of the die, resulting in corrosion of metal. The required pressure pot test time is 96-hours at a temperature of 121 degrees C and a pressure of to 2 atmosphere. The sample size is based on a LTPD = 3.

Temperature Cycling (Liquid to Liquid) - Temperature Cycling applies thermally-induced stress to the devices to accelerate material fatigue and to precipitate failures associated with thermal expansion mismatch and microcracks. The required total cycles are 500 cycles done per method 1011, Condition C (-65 C/ +150 C) of MIL-STD-883 (no bias). The minimum sample size is based on a LTPD = 3. (This test is optional)

Temperature Cycling (Air to Air) - Temperature Cycling applies thermally-induced stress to the devices to accelerate material fatigue and to precipitate failures associated with thermal expansion mismatch and microcracks for a longer period of test. The required total cycles is 500 cycles done per method 1010, Condition C (-65 C/+150 C) of MIL-STD-883. The minimum sample size is based on a LTPD = 3. For BGA, FBGA & CS packages, the required total cycles is 1000 cycles done per method 1010, Condition B (-55 C/+ 125C)



Bias Moisture test (85%R.H./85C) or HAST: 1 lot must be run and pass the Bias Moisture life. The required bias moisture life time at Xilinx is 1,000-hours minimum at 85 degrees C temperature, 85% relative humidity and nominal bias voltage. The sample size is based on LTPD = 3. HAST test is 100 hours minimum @ 130C/85%R.H. The sample size is 22 units.

Resistance to Solvents - This test evaluates the integrity of the package marking. At the present time this test is done outside the company at a qualified test laboratory. Test done per method 2015 of MIL-STD-883. The minimum sample size is 3 units and the allowable maximum reject units is 0.

Solderability - This test is performed to evaluate the integrity of the leads. At the present time this test is done outside the company per a qualified test laboratory. Test done per method 2003 of MIL-STD-883. The minimum sample size is 3 units (25 leads) and the allowable maximum reject units is 0.

Lead Fatigue - This test is performed to evaluate the integrity of the leads. At the present time test is done outside the company at a qualified test laboratory. Test done per method 2004 of MIL-STD-883. The minimum sample size is 3 units (25 leads) and the allowable maximum reject units is 0.

2.4.2<u>Hermetic Packages</u>: The hermetic package qualification requires a full group D test per MIL-STD-883, Method 5005.

2.5 **Reliability Monitor:** In addition to qualifying all new products and processes before going into production, Xilinx also runs periodic reliability monitors on existing production processes. The details of this monitor program are spelled out in Table I.



2.5.1<u>Process Monitor</u>: Xilinx fabrication processes are grouped into 16 families according to similarities in process and reliability characteristics and by fabrication facility. One or more products within these fabrication process families are selected as monitor vehicles. Process Monitor is run once a month with rotation of all 16 product families. Lot is tested with static burn-in (Refer to Table I for conditions and time).

2.5.2<u>Assembly Package Monitor</u>: Package types are grouped into families according to the package characteristics and assembly location. Two major categories, Plastic and Ceramic packages, are identified and each Package Family encompasses one or more lead counts.

Assembly Plastic Package Families are monitored once per quarter using a standard set of reliability tests listed in Table I. Monitor is run on separate packages from the Plastic Package families with rotation of all packages in the families.

3. <u>Reliability Families</u>: Xilinx products are manufactured in several worldwide locations. A limited number of process technologies are used for all product lines, resulting in manufacturing efficiency and significant experience with a particular process in different device applications. This strategy accelerates Xilinx's progress on the learning curve and results in process and products which are thoroughly characterized, inherently more reliable, and of the highest quality.

There are 16 different product families at Xilinx with various package combination: EPROM XC17XXX/L/E, XC17SXX,XC18VXX, Flash XC95XXX, XC95XXXL, CoolRunner (XCRXXXX) and LCA (Logic Cell Array); XC4XXX/E, XC4XXXEX, XC4XXXXL, XC4XXXLA, XCSXX, XC4XXXV, XCVXXXX, XCVXXXE, XC5XXX, XC2SXXX. Each product family has one or more products. These products are listed in Table II.

4. **Failure Analysis:** At Xilinx analysis is performed on all Qualification stress test failures, with the appropriate failure mechanism identified. For Failure analysis Xilinx uses the Failure Analysis Lab. in house Failure Analysis Lab. and outside subcontractors that are in constant contact with Design and product Engineering personnel. Each failure analysis is analyzed and categorized in accordance with the failure mechanism.



TABLE I					
STRESS	PURPOSE OF TEST	TYPICAL TEST PARAMETERS	SAMPLE FREQUENCY/ STRESS FAMILY		
High Temperature Operating Life (HTOL)	Determine major changes in device process, infant mortality levels	145 C Vcc = $5.7V$ or $3.3V$ for 256-hours, continuous bias applied. SS = 45 + 2 spares Accept 0	Monthly/Fab Process Family Assembly Package Family		
Extended Static Life Test	Determine device process durability to electrical and thermal stresses for long period of time	145 C Vcc = $5.7V$ or $3.3V$ for 2,000-hours, continuous basis applied. SS = $45 + 2$ spares Accept = 0	Quarterly/Fab Process Family		
Temperature Humidity (85/85)	Evaluate moisture resis- t`ance of die in plastic package	85 C @ 85% R.H. Vcc = 5.0V or 3.3V for 1,000-hrs, continuous bias applied. SS = LTPD 3	Quarterly/Fab Process Family Assembly Package Family		
Moisture Test	Test moisture resistance and integrity of plastic package	121 C @ 2 Atm. for 96-hours. SS = 45 Accept = 0	Quarterly/Assembly Package Family		
Thermal Shock (optional)	Evaluate resistance of the package to cracking and resistance of the bonding wires and leadframe separation	Cond. C, Method 1011 of MIL-STD-883, -65 C to +150 C for 500 Cycles Liquid to Liquid. $SS = 45$ Accept = 0	Quarterly/Fab Process Family Assembly Package Family		
Temperature Cycling	Detect mechanical reli- ability problems and thin film leakage caused by temperature change	Cond. C Method 1010 of MIL-STD-883, -65 C +150 C for 500 Cycles Air to Air. SS = 45 Accept = 0	Quarterly/Fab Process Family Assembly Package Family		



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TABLE I Continued

STRESS	PURPOSE OF TEST	TYPICAL TEST PARAMETERS	SAMPLE FREQUENCY/ STRESS FAMILY
Salt Atmosphere (Hermetics only)	Evaluate resistance to corrosion of the package finish and marking	Cond. A, Method MIL- STD-883, Method 1009, 24-hours. $SS = 15$ Accept = 0	Quarterly/Fab Process Family Assembly Package Family
Solderability	Evaluate the solderability of the leads under condi- tions of low soldering temperature following exposure to the aging effects of water vapor	MIL-STD-883, Method 2003. SS = 3 (25 Leads) Accept = 0	Quarterly/Fab Process Family Assembly Package Family
Mark Permanency	Evaluate the integrity of the package marking during exposure to a variety of solvents	MIL-STD-883, Method 2015. SS = 3 Accept = 0	Quarterly/Fab Process Family Assembly Package Family
Lead Fatigue	Evaluate the resistance of the completed assembly to vibrations during storage, shipping, and operations	MIL-STD-883, Method 2004. SS = 3 (25 Leads) Accept = 0	Quarterly/Fab Process Family Assembly Package Family
Physical Dimension	Verify that the external physical dimensions of the device are in accordance with the applicable procurement document	MIL-STD-883, Method 2015. SS = 15	Quarterly/Fab Process Family Assembly Package Family



TABLE II									
EPROM XC17XXD XC17XX/L/E	EPROM XC17SXX	EPROM XC18VXX	LCA XC4XXX/E	LCA XC4XXX/EX	LCA XC4>	4 KXXXL	LCA XC4XXX	XLA	LCA XC4XXXXV
XC1718D XC1736D XC1765D XC17128D XC17256D XC1701 XC1702 XC1704 XC1765E XC17256E	XC17S05/XL XC17S10/XL XC17S20/XL XC17S30/XL XC17S40/XL	XC18V01 XC18V02 XC18V04	XC4003/E XC4005/E XC4006/E XC4008/E XC4010/E XC4013/E XC4020/E XC4025/E	XC4028EX XC4036EX	XC40 XC40 XC40 XC40 XC40 XC40 XC40 XC40	005XL 010XL 020XL 028XL 036XL 036XL 044XL 052XL 062XL 085XL	XC4013 XC4020 XC4044 XC4028 XC4028 XC4036 XC4062 XC4062 XC4085	(LA (LA (LA (LA (LA (LA	XC40110XV XC40200XV XC40150XV XC40250XV
LCA XCSXX/XL	LCA	LCA XC2SXXX	LCA XCVXXX		XXE	Cool XCR	Runner xxxx	FL XC	ASH 95XXX/XL
XCS05/XL XCS10/XL XCS20/XL XCS30/XL XCS40/XL	XC5202 XC5204 XC5206 XC5210 XC5215	XC2S15 XC2S30 XC2S50 XC2S100 XC2S150 XC2S200	XCV50 XCV100 XCV150 XCV200 XCV300 XCV400 XCV600 XCV600 XCV800 XCV1000	XCV100 XCV200 XCV300 XCV400 XCV400 XCV600 XCV100 XCV100 XCV100 XCV100 XCV200 XCV320	0E 0E 0E 0E 0E 0E 0E 00E 00E 00E 00E	XCR XCR XCR XCR XCR XCR XCR XCR	3960 5064 3(5)032 3(5)064 3(5)128 22(L)V10 3256XL 3064XL 3128XL	XC XC XC XC XC	9536/XL 9572/XL 95108/XL 95216/XL 95288/XL
Oct 1 2000 B10									

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5. <u>Failure Acceleration Rates</u>: Since Xilinx uses accelerated stress tests in determining product failure rates, it is important to understand how the accelerated conditions are translated to standard operating conditions. Xilinx uses temperature acceleration techniques in which the thermal activation energy (Ea) is assigned for all failures mechanisms. FIT rates can be calculated from these data using the procedure for FIT rate calculation outlined below. The result will be the upper control limit expressed in Fits for the desired degree of confidence.

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 γ^2 10

Upper control limit expressed in Fits =

2(No. of dev.)(No. of hrs.) (acc. Factor)

Where χ^2 = tabular value of chi-squared distributions at the confidence level desired at (2f + 2) degress of freedom, where f is the number of failures.

The acceleration factor is calculated using the Arrhenius relationship

A = exp { Ea/k (1/Tj2 -1/Tj1) }

Ea = Thermal activation energy (electron Volts) A = Acceleration factor (0.9 Ev expressed in electron volts) K = Boltzman's constant {8.617164 x 10 exp (-5 ev/deg K)} Tj1 = In-use junction temperature in degrees Kelvin (Tin °K = T in °C + 273.16) Tj2 = In stress junction temperature in degrees Kelvin (Tin °K = T in °C + 273.16)

The in-use failure rate is the computed by dividing the in-stress failure rate by the acceleration factor

fr1 = fr2/A

fr1 = Failure rate at specified in-use junction temperature Tj1fr2 = Failure rate at specified in-stress junction temperature Tj2A = Acceleration factor

Notes: FIT = Failure Unit 1 FIT = 1 Failure / Billion device hours (1 x 10E09 failures) 1 FIT = 1 Failure / 10E+09 Device hours



TABLE III

F/A ACRONYM	DESCRIPTION	F/A ACRONYM	DESCRIPTION
ASL	Lifted Ball Bond	CMGL	Fine Leak at seal glass between Ceramic material
FANC	Failure Analysis not completed	CRCP	glass. Crack in the passivation
MST	Moisture in package	INC	Inconclusive
MARG	Marginal parametric failure	RAND	Random defect
NDF	No Defect found		
PFSM	Particle found in 2 Metal causing short	VCMD	defect
GAOD	Gate Oxide Defect	VUO	Via opened
MSKD	Mask defect		
WISIND	Wusk derect		



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Plastic Encapsulant Data (Typical)

	Test Conditions	6300HS	7320C	7304	MP8000CH4
Volume Resistivity (Ohm.cm)	150C	1 x 10 ¹³	1 x 10 ¹³	1 x 10 ¹³	5.5 x 10 ¹³
Water Absorption)	Boil 48 hrs (wt%)	0.3/24 hrs	0.22/24 hrs	0.25/24 hrs	0.3/48 hrs
Spiral Flow	(cm)	80	180	125	90cm
Ionic Impurities 160C x 23 hrs Extraction	Na+ (ppm)	<1	<1	<1	2
	CI - (ppm)	5	5	5	18
Flexural Strength (kgf/mm) ²	25C	12	17	17	17
Flexural Modulus (kgf/mm) ²	25C	1200	1750	1800	1900
Thermal Expansion (Cured @	α 1(1/C)	1.7 x 10 ⁻⁵	1.3 x 10⁵	1.4 x 10⁻⁵	1.2 x 10 ⁻⁵
175C for 5 hrs)	α 2(1/C)	6.8 x 10⁻⁵	5.2 x 10⁵	5.8 x 10⁵	4.9 x 10 ⁻⁵
Glass Transition -	Tg Range (C)	155 ~ 170C	130 ~ 155C	153 ~ 165C	156C ~ 160C



XILINX Typical I.R. Convection Oven Reflow



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Product Moisture Classification

PD-8	XC1700D/E & XC17SXX, XC18VXX	Level 1 / Unlimited
SO-8, SO-20	XC1700D/E & XC17SXX, XC18VXX	Level 1 / Unlimited
VO-8	XC1700D/E & XC17SXX, XC18VXX	Level 1 / Unlimited
PLCC (20, 44) PLCC (68)	ALL	Level 1 / Unlimited 90% Level 1 / Unlimited 10% Level 3
PLCC 84	ALL	30% Level 1 / Unlimited 70% Level 3 / 168 hours
PQFP (44, 100, 160, 208, 240)	ALL	Level 3 / 168 hours
TQFP (44, 100, 144, 176)	ALL	Level 3 / 168 hours
HQFP (160, 208, 240, 304)	ALL	Level 3 / 168 hours
VQFP (44, 64, 100)	ALL	Level 3 / 168 hours
HTQFP (144, 176, 208)	ALL	Level 3 / 168 hours
PPGA (132, 175)	ALL	Level 1 / Unlimited
CS (48, 144, 280)	ALL	Level 3 / 168 hours
CP (56)	XCR3064A/L	Level 3 / 168 hours
MQFP (208, 240)	ALL	Level 1 / Unlimited
BGA (225, 256)	ALL	Level 3 / 168 hours
SBGA (352, 432, 560, 728)	ALL	Level 3 / 168 hours
SBGA (560)	XC4085XL	Level 3 / 168 hours
FBGA (256, 456, 556, 676, 680, 900, 860, 1156)	XCVXXXX	Level 3 / 168 hours

Note (1): Classification for Plastic Integrated Circuit Surface Mount Devices, per J-STD-020



Latch-Up Data Per EIA/JEDEC-78

Device	Worst <u>Latch-Up</u>		Latch-Up Test Condition
XC17XXD/L	300mA Vcc +4.1V <-300mA Gnd -1.7V	>560mA Vcc +3.9V <-560mA Gnd -2.5V	25°C
XC17XXE XCS17XX	>300mA Vcc +4.1V to <-300mA Gnd -1.7V	>600mA Vcc +9.0V <-600mA Gnd -2.5V	25°C
XC3XXX/A	220mA Vcc +1.8V to <-300mA Gnd -1.8V	300mA Vcc +2.4V <-300mA Gnd -1.4V	25°C
XC31XX/A	300mA Vcc +1.5V <-300mA Gnd -1.3V		25°C
XC4XXX/A	300mA Vcc +2.6V <-300mA Gnd -1.4V		25°C
XC4XXXE	250mA Vcc +1.5V to <-250mA Gnd -1.7V	300mA Vcc +2.5V <-300mA Gnd -1.5V	25°C
XC4XXXXL	Vcc +3.4V** <-250mA Gnd -1.4V	Vcc +3.4V** <-550mA Gnd -1.55V	25°C
XC4XXXEX	250mA Vcc +1.8V to <-250mA Gnd -1.6V	0 400mA Vcc + 7.0V <-400mA Gnd -1.33	25°C

** The 5V tolerant I/O's used in the XL device are guaranteed not to sustain permanent damage when input is forced to maximum of 7V and with the forcing power supply being current limited to 200 mA.



Latch-Up Data Per EIA/JEDEC-78					
Device	Wor <u>Latch</u>	st -Up		Latch-Up Test Condition	
XC4XXXXLA	300mA Vcc +5.6V <-300mA Gnd -1.5V		460mA Vcc +7.0V <-460mA Gnd -2.0V	25°C	
XC4XXXXV	200mA Vcc +5.6V <-210mA Gnd -1.3V			25°C	
XCVXXXX	N/A <-210mA Gnd -1.2V		250mA Vcc +5.6V <-250mA Gnd -1.2V	25°C	
XCVXXXXE	210mA Vcc +5.3V <-210mA Gnd -1.10V		350 mA Vcc 3.9V -350mA Gnd -1.2V	25°C	
XCSXX	>410mA Vcc +8.1V <410mA Gnd -2.0V			25°C	
XCSXXXL	310mA Vcc +6.1V <-310mA Gnd -1.5V	to	410mA Vcc +6.5V <-410mA Gnd -1.9V	25°C	
XC5XXX	250mA Vcc +2.40V <-250mA Gnd -1.40V	to	350mA Vcc +2.35V <-400mA Gnd -2.20V	25°C	
XC95XXX	250mA Vcc +1.3V <-250mA Gnd -2.0V	to	600mA Vcc +7.2V <-600mA Gnd -1.70V	25°C	
XC95XXXL	350mA Vcc +2.8V <-525mA Gnd -0.53V			25°C	



ESD Data

	Human Body Model Worst Case ESD Mil-Std-883D	Machine Model Worst Case ESD EIAJ	Charge Device Model Worst Case ESD
Device	Method 3015	Method 20	
XC17XXXD	<u>+</u> 6000V	+500V to +900V	<u>+</u> 2000V (1)
XC17XXXE XCS17XXX	<u>+</u> 3000V to <u>+</u> 6000V	+325V	<u>+</u> 1000V (1)
XC31XX/A	<u>+</u> 1750V to <u>+</u> 8000V	+800V to +700V	<u>+</u> 1000V (3)
XC3XXX/A	<u>+</u> 4000V to <u>+</u> 7000V	+325V to +600V	<u>+</u> 2000V (2)
XC4XXX/A	<u>+</u> 1000V to <u>+</u> 8000V	+800V to +900V	<u>+</u> 2000V (4)
XC4XXXE	<u>+</u> 3000V to <u>+</u> 8000V		<u>+</u> 2000V (5)
XC4XXXEX	<u>+</u> 3000V to <u>+</u> 7000V		<u>+</u> 2000V (6)
XC4XXXXL	<u>+</u> 2000V to <u>+</u> 8000V	+1000V	<u>+</u> 1000V (7)
XC4XXXXLA	<u>+</u> 2000V to <u>+</u> 7000V		<u>+</u> 500V(Core)/ <u>+</u> 1000V(corner)(11)

(1) Measured on XC1765D, (2) Measured on XC3090, (3) Measured on XC3190/A, (4) Measured on XC4005

(5) Measured on XC4005E, (6) Measured on XC4010E, (7) Measured on XC4028XL (±1000V, Equipment limitation), (12) Measured on XC17256E

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ESD Data

	Human Body Model Worst Case ESD Mil-Std-883D	Machine Model Worst Case ESD EIAJ	Charge Device Model Worst Case ESD
Device	Method 3015	Method 20	
XCXXXXV	<u>+</u> 1500V to <u>+</u> 2000V		
XCVXXXX	<u>+</u> 1400V to <u>+</u> 1900V		
XCVXXXXE	<u>+</u> 2000V to <u>+</u> 3000V		
XCSXX	<u>+</u> 6000V		<u>+</u> 1000V (10)
XCSXXXL	<u>+</u> 3000V		<u>+</u> 500V (13)
XC5XXX	- <u>+</u> 3000V to <u>+</u> 7000V		<u>+</u> 2000V (8)
XC2SXXX	<u>+</u> 2000V		
XC95XXX	<u>+</u> 2000V to <u>+</u> 8000V		<u>+</u> 2000V (9)
XC95XXXL	<u>+</u> 2000V to <u>+</u> 6000V		<u>+</u> 1000V (12)
XCRXXXX	<u>+</u> 2000V to <u>+</u> 4000V		<u>+</u> 500V (14)
(8) Measured on X XC4062XLA, Meas	C5210, (9) Measured on 2 sured on XC9536XL, Meas	XC95108, (10) Measured on 2 sured on XCS30XL, Measure	XCS10 & XCS30, (11) Measured on d on XCR3064
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The FPGA Products



Technology:	Si Gate CMOS
Device Type:	XC3XXX/A, XC31XX/A, XC4XXX, XC4XXXE
Package Type:	Various
Actual Temperature	145C +8C/-0C
Actual Voltage:	5.7V +/-0.25
Assumed Activation Energy:	0.70 ev @ C.L. = 60%

XC3XXX/A

XC31XX/A

XC4XXXE

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XC4XXX

Period:	Oct. 1, 1998 to Oct. 1, 2000			
Combined Lots:	8	1	5	8
Failures:	0	0	0	0
Device on test:	364	45	223	352
Actual device hours:	307,159	46,485	158,146	289,256
Mean :	844	1,033	709	821
Equivalent device hours @ Tj=125C:	815,349	123,394	419,796	767,560
Equivalent device hours @ Tj=55C:	63,452,840	9,602,861	32,669,766	59,733,784
Equivalent device hours @ Tj=25C:	7.67E+08	1.16E+08	3.95E+08	7.22E+08
Failure Rate(60% C.L.) in FITS @ Tj=25C:	14	95	28	15
Failure Rate(60% C.L.) in FITS @ Tj=25C:	1	8	2	1

Technology:Si Gate CMOSDevice Type:XC4XXXEX, XC4XXXL, XCSXX,Package Type:VariousActual Temperature:145C +8C/-0CActual Voltage:3.6V +/-0.3**, 5.7V +/-0.25Assumed Activation Energy:0.70 ev @ C.L. = 60%

	XC4XXXEX	XC4XXXXL	XC4XXXXL Dynamic**	XCSXX
Period:	Oct.	1, 1998 to Oct. 1, 2000		
Combined Lots:	5	16	1	9
Failures:	0	0	0	1
Device on test:	312	611	43	371
Actual device hours:	169,487	589,006	152,908	386,935
Mean :	543	964	3,556	1,043
Equivalent device hours @ Tj=125C:	449,709	1,563,508	405,892	1,027,113
Equivalent device hours @ Tj=55C:	34,915,266	121,676,732	31,587,701	79,932,948
Equivalent device hours @ Tj=25C:	4.21E+08	1.47E+09	3.82E+08	9.66E+08
Failure Rate(60% C.L.) in FITS @ Tj=55C:	26	8	29	25
Failure Rate(60% C.L.) in FITS @ Tj=25C:	2	1	2	2

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Technology:Si Gate CMOSDevice Type:XCSXXXL, XC4XXXV, XC4XXXXLA, XCVXXXPackage Type:VariousActual Temperature:145C +8C/-0CActual Voltage:VariousAssumed Activation Energy:0.70 ev @ C.L. = 60%

XCSXXXL

XC4XXXXV

XC4XXXXLA XCVXXX

.<mark>€</mark>XILINX<u>®</u>

Period:	O	et. 1, 1998 to Oct. 1, 200	00	
Combined Lots:	8	2	8	21
Failures:	2	0	0	6
Device on test:	349	37	370	1,025
Actual device hours:	368,529	55,736	300,374	1,117,744
Mean :	1,056	1,506	812	1,090
Equivalent device hours @ Tj=125C:	978,255	147,950	797,338	2,967,035
Equivalent device hours @ Tj=55C:	76,130,641	11,513,931	62,051,196	230,903,313
Equivalent device hours @ Tj=25C:	9.20E+08	1.39E+08	7.50E+08	2.79E+09
Failure Rate(60% C.L.) in FITS @ Tj=25C:	41	80	15	32
Failure Rate(60% C.L.) in FITS @ Tj=25C:	3	7	1	3

Technology:Si Gate CMOSDevice Type:XCVXXX(dynamic),XC5XXX, XCVXXXE, XC2SXXXPackage Type:VariousActual Temperature:145C +8C/-0CActual Voltage:VariousAssumed Activation Energy:0.70 ev @ C.L. = 60%

XCVXXX Dynamic

XCVXXXE

XC2SXXX

XC5XXX

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Period:	Oct. 1, 1998 to Oct. 1, 2000			
Combined Lots:	2	12	5	7
Failures:	1	2	0	0
Device on test:	41	476	324	410
Actual device hours:	41,000	373,560	143,542	482,749
Mean :	1,000	785	443	1,177
Equivalent device hours @ Tj=125C:	108,834	830.355	381,030	1,281,450
Equivalent device hours @ Tj=55C:	8,469,771	64.620.655	29,652,875	99,276,184
Equivalent device hours @ Tj=25C:	1.02E+08	7.81E+08	3.59E+08	1.21E+09
Failure Rate(60% C.L.) in FITS @ Tj=55C:	239	48	31	9
Failure Rate(60% C.L.) in FITS @ Tj=25C:	20	4	3	1

Technology:	Si Gate CMOS
Device Type:	XC3XXX/A Microcircuit Group
Package Type:	PLCC- 84, PGA- 84
Actual Temperature:	145C +8C/-0C
Actual Voltage:	5.7V +/-0.25
Assumed Activation Energy:	0.70 ev @ C.L. = 60%

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	XC3020/A	XC3030/A	XC3042/A
Period:	Oct. 1,	1998 to Oct. 1, 2000	
Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C:	1 0 47 12,032 256 31,939 2,485,568 3.01E+07	2 0 90 93,510 1,039 248,221 19,317,275 2.34E+08	3 0 137 106,802 780 283,504 22,063,134 2.67E+08
Failure Analysis:			

Technology:	Si Gate CMOS
Device Type:	XC3XXX/A Microcircuit Group
Package Type:	PLCC- 84, PGA- 84
Actual Temperature:	145C +8C/-0C
Actual Voltage:	5.7V +/-0.25
Assumed Activation Energy:	0.70 ev @ C.L. = 60%

	XC3064/A	XC3090/A	XC3XXX/A
Period:	Oct. 1,	1998 to Oct. 1, 2000	
Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C:	1 0 45 46,035 1,023 122,129 9,509,900 1.22E+08	1 0 45 48,780 1,084 129,486 10,076,962 1.22E+08	8 0 364 307,159 844 815,349 63,452,840 7.67E+08
Failure Analysis:	Failure Rate (60% C.L.) in Failure Rate (60% C.L.) in	FITS @ Tj=55C: FITS @ Tj=25C:	14 1 ■■■■■■■■■■■■■■■■■■■■■■■■■■■■■■■■■■

Technology: Si Gate CMOS Device Type: XC31XX/A Microcircuit Group Package Type: PQFP-160 Actual Temperature: 145C +8C/-0C Actual Voltage: 5.7V +/-0.25 Assumed Activation Energy: 0.70 ev @ C.L. = 60%

XC3190/A

XC31XX/A

Period:	Oct. 1, 1998 to Oct. 1, 2000	
Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C:	1 0 45 46,485 1,033 123,341 9,576,169 1.16E+08	1 0 45 46,485 1,033 123,394 9,602,861 1.16E+08
Failure Analysis:		
Failure Rate (60% Failure Rate (60%	C.L.) in FITS @ Tj=55C: C.L.) in FITS @ Tj=25C:	95 8

Hi Qual	gh Temper lification &	ature Life T Monitor Comb	est oined	
Ac Assumed A	Technology: Device Type: Package Type: tual Temperature: Actual Voltage: Activation Energy:	Si Gate CMOS XC4XXX Microcircuit PLCC-84, PGA-156, 22 145C +8C/-0C 5.7V +/-0.25 0.70 ev @ C.L. = 60%	Group 23, PQFP-208	
	XC4005	XC4010/L	XC4013	XC4XXX
Period:	Oct.	1, 1998 to Oct. 1, 2000		
Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C:	2 0 92 60,812 661 161,425 12,562,530 1.52E+08	2 0 84 85,302 1,016 226,433 17,621,669 2.13E+08	1 0 47 12,032 256 31,939 2,485,568 3.01E+07	5 0 223 158,146 709 419,796 32,669,766 3.95E+08
Failure Analysis:	Failure Failure	Rate (60% C.L.) in FITS Rate (60% C.L.) in FITS	@ Tj=55C: @ Tj=25C:	28 2
				-{: XILINX

Oct. 1, 2000 P28

Technology:Si Gate CMOSDevice Type:XC4XXXE Microcircuit GroupPackage Type:PLCC-84, PGA-156, 191, 223, PQFP-208,240, HQFP-240Actual Temperature:145C +8C/-0CActual Voltage:5.7V +/-0.25Assumed Activation Energy:0.70 ev @ C.L. = 60%

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	XC4005E	XC40010E	XC4013E	XC4025E	XC4XXXE
Period:		Oct. 1, 1998 to Oc	ct. 1, 2000		
Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C: Failure Analysis:	1 0 45 48,780 1,084 129,486 10,076,962 1.22E+08	1 0 47 12,032 256 31,939 2,485,568 3.01E+07	5 0 218 177,524 814 471,235 36,672,869 4.43E+08	1 0 42 50,820 1,210 134,901 10,498,385 1.27E+08	8 0 352 289,256 821 767,560 59,733,784 7.22E+08
		Failure Rate Failure Rate	(60% C.L.) in FI (60% C.L.) in FI	ΓS @ Tj=55C: ΓS @ Tj=25C:	15 1

Technology:	Si Gate CMOS
Device Type:	XC4XXXEX Microcircuit Group
Package Type:	HQFP-240, 208
Actual Temperature:	145C +8C/-0C
Actual Voltage:	5.7V +/-0.25
Assumed Activation Energy:	0.70 ev @ C.L. = 60%

XC4028EX

XC4XXXEX

Period:	Oct. 1, 1998 to Oct. 1, 2000	
Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C: Failure Analysis:	5 0 312 169,487 543 449,901 35,012,588 4.23E+08	5 0 312 169,487 543 449,901 35,012,588 4.23E+08
Failure Rate (60%) Failure Rate (60%)	C.L.) in FITS @ Tj=55C: C.L.) in FITS @ Tj=25C:	26 2

Technology:	Si Gate CMOS
Device Type:	XC4XXXXL Microcircuit Group
Package Type:	PLCC-84, PGA- 411, 475 , 559, HQFP-208, 240
	PQFP-208, CB228
Actual Temperature:	145C +8C/-0C
Actual Voltage:	3.6V +/-0.3
Assumed Activation Energy:	0.70 ev @ C.L. = 60%

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	XC4005XL	XC4013XL	XC4028XL	XC4036XL
Period:		Oct. 1, 1998 to Oct. 1, 2000		
Combined Lots:	1	5	2	2
Failures:	0	0	0	0
Device on test:	43	229	83	87
Actual device hours:	66,478	162,619	83,205	88,191
Mean :	1,546	710	1,002	1,014
Equivalent device hours @ Tj=125C:	176,465	431,670	220,866	234,102
Equivalent device hours @ Tj=55C:	13,733,011	33,593,798	17,188,471	18,218,478
Equivalent device hours @ Tj=25C:	1.66E+08	4.06E+08	2.08E+08	2.20E+08

Failure Analysis:

Technology:	Si Gate CMOS
Device Type:	XC4XXXXL Microcircuit Group
Package Type:	PLCC-84, PGA- 411, 475 , 559, CB-228, HQFP-208, 240
	PQFP-208,
Actual Temperature:	145C +8C/-0C
Actual Voltage:	3.6V +/-0.3
Assumed Activation Energy:	0.70 ev @ C.L. = 60%

XC4044XL XC4052XL

052XL XC4062XL

XC4085XL XC4XXXL

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Period:	Oct. 1, 1998 to Oct. 1, 2000				
Combined Lots:	1	1	4	2	16
Failures:	0	0	0	0	0
Device on test:	22	22	125	63	611
Actual device hours:	21,736	22.022	144,755	56,016	589,006
Mean :	988	1.001	1,158	889	964
Equivalent device hours @ Tj=125C:	57,698	58.457	294,250	148,694	1,563,508
Equivalent device hours @ Tj=55C:	4,490,218	4.549.300	29,903,456	11,571,773	121,676,732
Equivalent device hours @ Tj=25C:	5.43E+07	5.50E+07	3.62E+08	1.40E+08	1.47E+09
Failure Analysis:		Failure Ra	te (60% C.L.) in FI	TS @ Ti=55C:	8
		Failure Ra	te (60% C.L.) in FI	TS @ Tj=25C:	1

Si Gate CMOS
XC4XXXXLA Microcircuit Group
PGA-223, HQFP-208, 240
145C +8C/-0C
3.6V +/-0.3
0.70 ev @ C.L. = 60%

XC4036XLA

XC4044XLA

XC4062XLA

• **{ `** XILINX®

Period:	Period: Oct. 1, 1998 to Oct. 1, 2000		
Combined Lots:	2	1	3
Failures:	0	0	0
Device on test:	120	42	125
Actual device hours:	63,076	44,394	106,922
Mean :	526	1,057	855
Equivalent device hours @ Tj=125C:	167,434	117,843	283,823
Equivalent device hours @ Tj=55C:	13,030,226	9,170,903	22,087,924
Equivalent device hours @ Tj=25C:	1.58E+08	1.11E+08	2.67E+08

Failure Analysis:

Technology:Si Gate CMOSDevice Type:XC4XXXXLA Microcircuit GroupPackage Type:PGA-223, HQFP-208, 240Actual Temperature:145C +8C/-0CActual Voltage:3.6V +/-0.3Assumed Activation Energy:0.70 ev @ C.L. = 60%

XC4085XLA

XC40XXXLA

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Period:	Oct. 1	, 1998 to Oct. 1, 2000
Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C:	2 0 83 85,982 1,036 228,238 17,762,143 2.15E+08	8 0 370 300,374 812 797,338 62,051,196 7.50E+08
Failure Analysis:		Failure Rate (60% C.L.) in FITS @ Tj=55C: 15 Failure Rate (60% C.L.) in FITS @ Tj=25C: 1

Technology:Si Gate CMOSDevice Type:XC4XXXL Microcircuit GroupPackage Type:PLCC-84Actual Temperature:145C +8C/-0CActual Voltage:3.6V +/-0.3Assumed Activation Energy:0.70 ev @ C.L. = 60%

XC4005XL

XC4XXXXL

Dynamic

Period:	Oct. 1, 1998 to Oct. 1, 2000	
Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C:	1 0 43 152,908 3,556 405,892 31,587,701 3.82E+08	1 0 43 152,908 3,556 405,892 31,587,701 3.82E+08
Failure Analysis: Failure Failure	Rate (60% C.L.) in FITS @ Tj=55C: Rate (60% C.L.) in FITS @ Tj=25C:	29 2

H Q	Reliabili Iigh Temp Jualificatio	ty Testing erature Op n & Monit	Summary perating Life or Combine	e ed	
Assu	Techn Device Package Actual Temper Actual Vo ned Activation E	ology: Si Gate (Type: XCSXX Type: PLCC-84 ature: 145C +86 oltage: 3.6V +/-(nergy: 0.70 ev @	CMOS Microcircuit Group 4, PGA- 223, PQFP C/-0C).3 © C.L. = 60%	-240	
	XCS10	XCS20	XCS30	XCS40	XCSXX
Period:		Oct. 1, 1998 to	Oct. 1, 2000		
Combined Lots:	1	1	5	2	9
Failures:	0	0	1	0	1
Device on test:	45	42	202	82	371
Actual device hours:	49,860	42,714	212,361	82,000	386,835
Mean :	1,108	1,017	1,051	1,000	1,043
Equivalent device hours @ Tj=125C:	132,353	113,384	563,709	217,668	1,027,113
Equivalent device hours @ Tj=55C:	10,300,068	8,823,849	43,869,489	16,939,542	79,932,948
Equivalent device hours @ Tj=25C:	1.25E+08	1.07E+08	5.30E+08	2.05E+08	9.66E+08
			F/A99119(1)-INC		
Failure Analysis:		Failure Ra	te (60% C.L.) in FI	TS @ Ti=55C:	25
		Failure Ra	te (60% C.L.) in FI	TS @ Tj=25C:	2
Failure Analysis:		Failure Ra Failure Ra	F/A99119(1)-INC ate (60% C.L.) in FI ate (60% C.L.) in FI	TS @ Tj=55C: TS @ Tj=25C:	25 2
Reliability Testing Summary High Temperature Operating Life Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XCSXXXL Microcircuit Group
Package Type:	PGA- 191, 223, PQFP-208, PLCC-84
Actual Temperature:	145C +8C/-0C
Actual Voltage:	3.6V +/-0.3
Assumed Activation Energy:	0.70 ev @ C.L. = 60%

XCS05XL

XCS10XL

XCS20XL

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Period:	Oct. 1, 1998 to Oct. 1, 2000			
Combined Lots:	1	1	3	
Dovice on test:	0	0	4	
Device on test.	45	44	104	
Actual device hours:	50,715	49,588	107,900	
Mean :	1.127	1,127	1,038	
Equivalent device hours @ Tj=125C:	134.622	131,631	286,419	
Equivalent device hours @ Tj=55C:	10.476.694	10,243,878	22,289,959	
Equivalent device hours @ Tj=25C:	1.27E+08	1.24E+08	2.69E+08	
Failure Analysis:			F/A98139(2)-RAND	

	Reliability To High Temperate Qualification &	esting Summary ure Operating Life Monitor Combined	
	Technology: Device Type: Package Type: Actual Temperature: Actual Voltage: Assumed Activation Energy:	Si Gate CMOS XCSXXXL Microcircuit Group PGA- 191, 223, PQFP-208, PLCC 145C +8C/-0C 3.6V +/-0.3 0.70 ev @ C.L. = 60%	-84
	XCS30XL	XCS40XL	XCSXXXL
Period	: Oct.	1, 1998 to Oct. 1, 2000	
Combined Lots Failures Device on test: Actual device hours Mean Equivalent device hours @ Tj=125C Equivalent device hours @ Tj=55C Equivalent device hours @ Tj=25C Failure Analysis	1 0 72 72,000 1,000 191,123 14,873,744 1.80E+08	2 0 84 88,326 1,052 234,460 18,246,366 2.21E+08	8 2 349 368,529 1,056 978,255 76,130,641 9.20E+08
	Failure Rate (60% C.I Failure Rate (60% C.I	2.) in FITS @ Tj=55C: 2.) in FITS @ Tj=25C:	41 3 \$* XII INIX ®

H Qu	Reliability To igh Temperat ualification &	esting Sum ure Operat Monitor Co	mary ing Life ombined	
Assum	Technology: Device Type: Package Type: Actual Temperature: Actual Voltage: aed Activation Energy:	Si Gate CMOS XC2SXXX Micr PQFP-208 145C +8C/-0C 2.7V (Core);3.7V 0.70 ev @ C.L. =	ocircuit Group 7(I/O) 60%	
	XC2S50	XC2S100	XC2S150	XC2SXXX
Period:	Oct.	1, 1998 to Oct. 1, 2	000	
Combined Lots:	1	1	3	5
Failures:	0	0	0	0
Device on test:	76	76	172	324
Actual device hours:	13,604	13,908	116.030	143,542
Mean :	179	183	675	443
Equivalent device hours @ Tj=125C:	36,112	36,919	308,000	381,030
Equivalent device hours @ Tj=55C:	2,810,311	2,873,112	23,969,452	29,652,875
Equivalent device hours @ Tj=25C:	3.40E+07	3.47E+07	2.90E+08	3.59E+08
Failure Analysis:				
	Failura Dat	e (60% C I) in FI	TS @ Ti-55C•	31
	Failure Rat	e (60% C.L.) in FI	TS @ Tj=25C:	3
				<u> </u>

Reliability Testing Summary High Temperature Operating Life Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XC4XXXXV Microcircuit Group
Package Type:	PG-599
Actual Temperature:	145C +8C/-0C
Actual Voltage:	2.625V (Core);3.6V(I/O)
Assumed Activation Energy:	0.70 ev @ C.L. = 60%

	XC40110XV	XC40150XV	XC4XXXXV
Period:	Oct. 1, 1998 t	o Oct. 1, 2000	
Combined Lots: Failures:	1 0	1	2
Device on test:	15	22	37
Actual device hours:	32,460	23,276	55,736
Mean :	2,164	1,058	1,506
Equivalent device hours @ Tj=125C:	86,165	61,786	147,950
Equivalent device hours @ Tj=55C:	6,705,580	4,808,351	11,53,931
Equivalent device hours @ Tj=25C:	8.11E+07	5.81E+07	1.39E+08
Failure Analysis:	Failure Rate (60% C.L.) in	n FITS @ Tj=55C:	80
	Failure Rate (60% C.L.) in	n FITS @ Tj=25C:	7
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			K ANLINA

Assu	Reliabi High Te Tech Device Package Actual Tempe Actual V ned Activation E	lity Testing emperature Qualificatio nology: Si Gate C Type: XCVXXX Type: HQFP-24 erature 145C +8C oltage: 2.625V (C energy: 0.70 ev @	Summary Life Test DN MOS Microcircuit Gro 0, PQFP-240 Z-0C Core); 3.6V (I/O) C.L. = 60%	up	
	XCV50	XCV100	XCV150	XCV200	XCV300
Period:		Oct. 1, 1998 to	Oct. 1, 2000		
Combined Lots:	1	1	1	2	6
Failures:	0	0	0	1	2
Device on test:	66	76	76	152	423
Actual device hours:	33,000	76,836	39,216	153,374	487,019
Mean :	500	1,011	516	1,009	1,151
Equivalent device hours @ Tj=125C:	87,598	203,960	104,098	407,129	1,292,785
Equivalent device hours @ Tj=55C:	6,817,133	15,872,764	8,101,233	31,683,968	100,608,279
Equivalent device hours @ Tj=25C:	8.24E+07	1.92E+08	9.79E+07	3.83E+08	1.22E+09
Failure Analysis:				F/A99095(1)-NDF	F/A99029(1)-INC FA00072(1)-RAND
					XILINX [®]

	Relia High To De Pacl Actual Te Actual	bility Te Tempera Quali echnology: wice Type: kage Type: mperature al Voltage:	esting Sum ature Life fication Si Gate CMOS XCVXXX Microo HQFP-240, PQFI 145C +8C/-0C; 12 2.625V (Core); 3.0	mary e Test circuit Group 2-240, *BG560 25C* 6V (I/O)		
Ass	umed Activatio	on Energy:	0.70 ev @ C.L. =	60%		
	XCV400	XCV60	0 XCV8	00 X	CV1000	XCVXXX
Period:		Oct. 1	l, 1998 to Oct. 1, 2	2000	*	
Combined Lets:		•	3	4	* 1	21
Combined Lois: Failures:	1	2	3	4	0	6
Device on test:	076	1	0 49	63	5	1,025
Actual device hours:	/0 114 000	44 65 561	61 523	90.328	1.884	1,117,744
Mean :	114,000	05,504	1.256	1.434	377	1,090
Equivalent device hours @ Ti=125C:	302 611	1,490	163.312	239,774	5,001	2,967,035
Equivalent device hours @ Tj=55C:	23.550.095	13.544.197	12,709,408	18,659,939	389,196	230,903,313
Equivalent device hours @ Tj=25C:	2.85E+08	1.64E+08	1.54E+08	2.26E+08	4.71E+06	2.79E+09
Failure Analysis:	F/	A 00025(1)-FANC		F/A99035(2)-NDF		
		Failure Rate((60% C.L.) in FIT	TS @ Tj=55C:		32
		Failure Rate	60% C.L.) in FI1	TS @ Tj=25C:		3
					{	

Reliability Testing Summary High Temperature Operating Life Qualification & Monitor Combined

Technology:Si Gate CMOSDevice Type:XCVXXX Microcircuit GroupPackage Type:PQFP-240Actual Temperature:145C +8C/-0CActual Voltage:2.625V (Core); 3.6V (I/O)Assumed Activation Energy:0.70 ev @ C.L. = 60%

XCV300

XCVXXX

Dynamic

Period:	Oct. 1, 1998 to Oct. 1, 2000	
Combined Lots:	2	2
Failures:	1	0
Device on test:	41	41
Actual device hours:	41,000	41,000
Mean :	1,000	1,000
Equivalent device hours @ Tj=125C:	108,834	108,834
Equivalent device hours @ Tj=55C:	8,469,771	8,469,771
Equivalent device hours @ Tj=25C:	1.02E+08	1.02E+08
Failure Analysis:	F/A00084(1)-FANC	
		239
Failure Rate	(60% C.L.) in FITS @ Tj=55C:	20
Failure Rate	(60% C.L.) in FITS @ Tj=25C:	
		€* ∨II INIV®

	Reliabi High T	ility Test emperat Qualifi nology: Si	ting Sur ture Li cation Gate CMOS	nmary fe Test	
Ass	Devic Packag Actual Temp Actual V umed Activation I	e Type: XC ge Type: HC erature 14 Voltage: 2.2 Energy: 0.7	CVXXXE Mi (FP-240, PQ) 5C +8C/-0C, (V (Core); 3.0 (0 ev @ C.L.	crocircuit Group FP-240, BG560 *125C 6V (I/O) = 60%	
	XCV300E	XCV	1000E	XCV2000E	XCVXXXE
Period:		Oct. 1, 1	998 to Oct. 1	, 2000	
Combined Lots:	5	1	*4	*3	13
Failures:	2	0	0	0	2
Device on test:	340	22	78	60	500
Actual device hours:	253,941	22,154	23,917	18,144	318,156
Mean :	747	1,007	814	802	636
Equivalent device hours @ Tj=125C:	674,083	58,807	63,459	48,142	844,540
Equivalent device hours @ Tj=55C:	52,459,077	4,576,569	4,940,769	3,748,184	65,724,597
Equivalent device hours @ Tj=25C:	6.34E+08	5.53E+07	5.97E+07	4.53E+07	7.95E+08
Failure Analysis:	F/A99262(1)-GAOD F/A00061(1)-MSKD				
		F: F:	ailure Rate(6 ailure Rate(6	50% C.L.) in FITS @ 50% C.L.) in FITS @	2 Tj=55C: 47 2 Tj=25C: 4
					{XILINX ®

	Reliabili High Ter Qualificatio	ty Testing Summ nperature Life n & Monitor Co	nary Test ombined	
As	Techn Device Package Actual Temper Actual Ve sumed Activation E	ology:Si Gate CMOSType:XC5XXX MicrocType:PLCC-84, PGA-2rature:145C +8C/-0Coltage:5.7V +/-0.25nergy:0.70 ev @ C.L. =	ircuit Group 23, PQFP-208, 240 60%	
	XC5202	XC5204	XC5210	XC5XXX
Period:		Oct. 1, 1998 to Oct. 1, 20	000	
Combined Lots:	1	2	4	7
Failures:	0	0	0	0
Device on test:	45 40 700	129 107 220	250	41U 102 710
Actual device hours:	4ð,/ðu 1 ng <i>i</i>	17/,237 1 520	230,/3U 1 AA2	402,/49 1 177
Mean :	1,004 129 431	1,547 523 568	1,003 678 306	1,177
Equivalent device hours @ Tj=125C:	10.048.952	40.745.590	48,903.632	99.726.184
Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C:	1.21E+08	4.93E+08	5.91E+08	1.21E+09
Failure Analysis:		Failure Rate (60% C.L.) in Failure Rate (60% C.L.) in	n FITS @ Tj=55C: n FITS @ Tj=25C:	9 1
				_{XILINX ®

	Reliability T Bi Qualificati	esting Summa as Moisture L on & Monitor	ary-Packages ife Combined			
Technology:Si Gate CMOSDevice Type:XC3XXX/A, XC4XXX/E, XC4XXXLPackage Type:VariousTest Condition:T=85C, R.H.=85%Bias Voltages:5.0V +/25V* 3.3V +/-0.3V**2.7V +/3V						
	XC3XXX/A	XC4XXX	XC4XXXE	XC4XXXXL*		
Period:		Oct. 1, 1998 to Oct	. 1, 2000			
Combined Started Lot:	3	2	4	7		
Combined Completed Lots:	3	2	4	7		
Failures:	0	0	0	0		
Device on test:	140	150	131	230		
Mean Test Hour s/Device:	1,068	903	1,141	1,009		
Total Device Hours:	149,530	135,484	149,526	232,026		

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Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined				
Technology: Si Gate CMOS Device Type: XC4XXXLA, XCVXXX, XCSXXXL, XCSXX, Package Type: Various Test Condition: T=85C, R.H.=85% Bias Voltages: 5.0V +/25V * 3.3V +/-0.3V **2.7V +/3V				
	XC4XXXXLA*	XCVXXX**	XCSXXXL	XCSXX
Period:		Oct. 1, 1998 to Oct. 1	, 2000	
Combined Started Lot:	3	3	1	1
Combined Completed Lots:	3	3	1	1
Failures:	0	0	0	0
Device on test:	126	119	11	45
Mean Test Hour s/Device:	1,026	1,098	1,019	1,000
Total Device Hours:	129,256	130,691	11,209	45,000
				—{{` XILINX®

Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined				
	Technology: Device Type: Package Type: Test Condition: Bias Voltages:	Si Gate CMOS XC3XXX/A Microcir PQFP-100, VQFP-64 T = 85C, R.H. = 85% 5.0V +/25V	cuit Group , 44	
	XC3030/A	XC3042/A	XC3XXX/A	
Period:	Oct.	1, 1998 to Oct. 1, 2000		
Combined Started Lot:	2	1	3	
Combined Completed Lots:	2	1	3	
Failures:	0	0	0	
Device on test:	95	45	140	
Mean Test Hour s/Device:	1,045	1,117	1,068	
Total Device Hours:	99,265	50,265	149,530	
Failure Analysis Number:			€`XILINX®	

Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XC4XXX Microcircuit Group
Package Type:	BGA-225, PQFP- 240
Test Condition:	T = 85C, R.H. = 85%
Bias Voltages:	5.0V +/25V

XC4XXX

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XC4013

Period:	Oct. 1, 1998 to Oct.	1, 2000
Combined Started Lot:	2	2
Combined Completed Lots:	2	2
Failures:	0	0
Device on test:	150	150
Mean Test Hour s/Device:	903	903
Total Device Hours:	135,484	135,484
Failure Analysis Number:		

Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined Technology: Si Gate CMOS Device Type: XC4XXXE Microcircuit Group Package Type: PQFP-208, 240, PLCC-84 Test Condition: T = 85C, R.H. = 85% Bias Voltages: 5.0V +/25V					
	XC4006E	XC4010E	XC4013E	XC4025E	XC4XXXE
Period:		Oct. 1, 19	98 to Oct. 1, 2000		
Combined Started Lot:	1	1	1	1	4
Combined Completed Lots:	1	1	1	1	4
Failures:	0	0	0	0	0
Device on test:	21	45	43	22	131
Mean Test Hour s/Device:	1,000	1,148	1,234	1,082	1,141
Total Device Hours:	21,000	51,660	53,062	23,804	149,526
Failure Analysis Number:					=€`XILINX [®]

	Reliability Testing Bias Mo Qualification &	g Summary-Pa Disture Life Monitor Comb	ckages oined
	Technology: Device Type: Package Type: Test Condition: Bias Voltages:	Si Gate CMOS XC4XXXXL Microciro BGA-560, PQFP-240, I T = 85C, R.H. = 85% 3.3V +/3V	cuit Group HT-144, PLCC-84
	XC4010XL	XC4013XL	XC4020XL
Period:	July	1, 1998 to July 1, 2000	
Combined Started Lot:	1	1	2
Combined Completed Lots:	1	1	2
Failures:	0	0	0
Device on test:	45	45	90
Mean Test Hour s/Device:	1,006	1,019	935
Total Device Hours:	45,270	45,855	84,105
Failure Analysis Number:			
			€XILINX®

Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined			
	Technology: Device Type: Package Type: Test Condition: Bias Voltages:	Si Gate CMOS XC4XXXL Microcircuit Group BGA-560, PQFP-240, HT-144, PLCC-4 T = 85C, R.H. = 85% 3.3V +/3V	84
	XC4062XL	XC4085XL	XC4XXXXL
Period:	Oct.	1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	2	7
Combined Completed Lots:	1	2	7
Failures:	0	0	0
Device on test:	14	36	230
Mean Test Hour s/Device:	1,008	1,186	1,009
Total Device Hours:	14,112	42,684	232,026
Failure Analysis Number:			_\$`XILINX®

	Reliability Testing Bias Mo Qualification &	g Summary-Packages Disture Life Monitor Combined	
	Technology: Device Type: Package Type: Test Condition: Bias Voltages:	Si Gate CMOS XC4XXXLA Microcircuit Group HQFP- 240, PQFP- 240 T = 85C, R.H. = 85% 3.3V +/3V	
	XC4013XLA	XC4062XLA	XC4XXXXLA
Period:	Oct.	1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	2	3
Combined Completed Lots:	1	2	3
Failures:	0	0	0
Device on test:	37	89	126
Mean Test Hour s/Device:	1,071	1,007	1,026
Total Device Hours:	39,627	89,629	129,256
Failure Analysis Number:			\$`XILINX®

	Reliability Testing Bias Mo Qualification &	g Summary-Packages Disture Life Monitor Combined	
	Technology: Device Type: Package Type: Test Condition: Bias Voltages:	Si Gate CMOS XCVXXX Microcircuit Group CS-144, TQFP-144, BGA-432 T = 85C, R.H. = 85% 2.7V +/3V	
	XCV100	XCV800	XCVXXX
Period:	Oct.	1, 1998 to Oct. 1, 2000	
Combined Started Lot:	2	1	3
Combined Completed Lots:	2	1	3
Failures:	0	0	0
Device on test:	103	16	119
Mean Test Hour s/Device:	1,088	1,166	1,098
Total Device Hours:	112,035	18,656	130,691
Failure Analysis Number:			€_XILINX®

	Reliability Testing Bias Mo Qualification &	g Summary-Packages Disture Life Monitor Combined	
	Technology: Device Type: Package Type: Test Condition: Bias Voltages:	Si Gate CMOS XCSXX Microcircuit Group PQFP-240 T = 85C, R.H. = 85% 5.07V +/25V	
	XCS30		XCSXX
Period:	Oct.	1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1		1
Combined Completed Lots:	1		1
Failures:	0		0
Device on test:	45		45
Mean Test Hour s/Device:	1,000		1,000
Total Device Hours:	45,000		45,000
Failure Analysis Number:			
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Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XCSXXXL Microcircuit Group
Package Type:	TQFP-144
Test Condition:	T = 85C, R.H. = 85%
Bias Voltages:	3.3V +/3V

XCS30XL

XCSXXXL

Period:	Oct. 1, 1998 to Oct. 1,	, 2000
Combined Started Lot:	1	1
Combined Completed Lots:	1	1
Failures:	0	0
Device on test:	11	11
Mean Test Hour s/Device:	1,019	1,019
Total Device Hours:	11,209	11,209
Failure Analysis Number:		
		{XILINX [®]

	Reliability 7 Qualificat	Festing Summa Pressure Pot ion & Monitor	ry-Packages Combined	
	Tec Dev Packa Test C	chnology: Si Gate CMC ice Type: XC3XXX/A, age Type: Various ondition: T=121C; 2 at	DS XC31XX/A, XC4XX m. sat. steam	XX/E
	XC3XXX/A	XC31XX/A	XC4XXX	XC4XXXE
Period:		Oct. 1, 1998 to Oct.	1, 2000	
Combined Started Lot:	4	1	5	10
Combined Completed Lots:	4	1	5	10
Failures:	0	0	0	0
Device on test:	210	45	261	383
Mean Test Hour s/Device:	129	96	104	115
Total Device Hours:	27,120	4,320	27,144	44,112
				€_XILINX [®]

Reliability Testing Summary-Packages Pressure Pot Qualification & Monitor Combined					
	Technology:Si Gate CMOSDevice Type:XCSXXXL, XC4XXXL, XCXXXXVPackage Type:VariousTest Condition:T=121C; 2 atm. sat. steam				
	XCSXXXL	XC4XXXXL	XCXXXXV		
Period:	O	Oct. 1, 1998 to Oct. 1, 2000			
Combined Started Lot:	4	12	2		
Combined Completed Lots:	4	12	2		
Failures:	0	0	0		
Device on test:	173	380	59		
Mean Test Hour s/Device:	152	115	96		
	26 252				

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Technology:	Si Gate CMOS
Device Type:	XC4XXXXV,XC4XXXXLA, XCVXXX
Package Type:	Various
Test Condition:	T=121C; 2 atm. sat. steam

XC4XXXXLA

XCVXXX

XCVXXXXE

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Period:	Oct. 1, 1998 to Oct. 1, 2000			
Combined Started Lot:	5	10	6	
Combined Completed Lots:	5	10	6	
Failures:	0	0	0	
Device on test:	170	439	142	
Mean Test Hour s/Device:	132	132	149	
Total Device Hours:	22,512	57,984	21,192	

Technology:Si Gate CMOSDevice Type:XC3XXX/A Microcircuit GroupPackage Type:PLCC-44, 68, VQFP-64Test Condition:T = 121C; 2 atm. sat. steam.

XC3XXX/A

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XC3030/A

Period:	Oct. 1, 1998 to Oct. 1,	2000
Combined Started Lot:	4	4
Combined Completed Lots:	4	4
Failures:	0	0
Device on test:	210	210
Mean Test Hour s/Device:	129	129
Total Device Hours:	27,120	27,120
Failure Analysis Number:		

Technology:Si Gate CMOSDevice Type:XC31XX/A Microcircuit GroupPackage Type:TQFP-176Test Condition:T = 121C; 2 atm. sat. steam.

XC3190/A

XC31XX/A

Period:	Oct. 1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	1
Combined Completed Lots:	1	1
Failures:	0	0
Device on test:	45	45
Mean Test Hour s/Device:	96	96
Total Device Hours:	4,320	4,320
Failure Analysis Number:		
		€ XILINX [®]

Reliability Testing Summary-Packages Pressure Pot Qualification & Monitor Combined					
	Tech Device Packag Test Cor				
	XC4006	Σ	KC4010	XC4013	XC4XXX
Period:		Oct.	1, 1998 to Oct. 1	1, 2000	
Combined Started Lot:	1		2	2	5
Combined Completed Lots:	1		2	2	5
Failures:	0		0	0	0
Device on test:	44		65	152	261
Mean Test Hour s/Device:	96		72	120	104
Total Device Hours:	4,224		4,680	18,240	27,144
Failure Analysis Number:					
					_{XILINX ®

Technology:Si Gate CMOSDevice Type:XC4XXXE Microcircuit GroupPackage Type:HQFP-240, PQFP-208, 240, VQFP-100Test Condition:T = 121C; 2 atm. sat. steam

	XC4003E	XC4010E	XC4013E	XC4025E	XC4XXXE
Period:		Oct. 1, 1998	to Oct. 1, 2000		
Combined Started Lot:	1	1	3	5	10
Combined Completed Lots:	1	1	3	5	10
Failures:	0	0	0	0	0
Device on test:	44	35	108	196	383
Mean Test Hour s/Device:	168	96	111	109	115
Total Device Hours:	7,392	3,360	11,952	21,408	44,112
Failure Analysis Number:					
					\$ *XILINX <u>®</u>

Technology:	Si Gate CMOS
Device Type:	XCSXXXL Microcircuit Group
Package Type:	VQFP-100, TQFP-144, CS-280
Test Condition:	T = 121C; 2 atm. sat. steam

	XCS30XL	XCS40XL	XCSXXXL
Period:	Oct.	1, 1998 to Oct. 1, 2000	
Combined Started Lot:	3	1	4
Combined Completed Lots:	3	1	4
Failures:	0	0	0
Device on test:	132	41	173
Mean Test Hour s/Device:	170	96	152
Total Device Hours:	22,416	3,936	26,352
Failure Analysis Number:			
			 {XILINX

Reliability Testing Summary-Packages Pressure Pot Qualification & Monitor Combined					
	Technology:Si Gate CMOSDevice Type:XC4XXXL Microcircuit GroupPackage Type:PQFP-240, BGA-256,352, 432, 560TQFP-176, HT-144Test Condition:T = 121C; 2 atm. sat. steam				
	XC4010XL	XC4013XL	XC4020XL	XC4036XL	
Period:	Oct.	1, 1998 to Oct. 1, 2000			
Combined Started Lot:	2	2	1	3	
Combined Completed Lots:	2	2	1	3	
Failures:	0	0	0	0	
Device on test:	121	90	20	32	
Mean Test Hour s/Device:	141	96	96	96	
Total Device Hours:	17,088	8,640	1,920	3,072	
Failure Analysis Number:					
				=&XILINX®	

	Reliability Testing Summary-Packages Pressure Pot Qualification & Monitor Combined					
	Technol Device T Package T Test Condit	ogy: Si Gate CM0 ype: XC4XXXXI ype: PQFP-240, F TQFP-176, I tion: T = 121C; 2	OS 2 Microcircuit Group 3GA-256,352, 432, 560 HT-144, PLCC-84 atm. sat. steam			
	XC4052XL	XC4062XL	XC4085XL	XC4XXXXL		
Period:		Oct. 1, 1998 to Oct.	. 1, 2000			
Combined Started Lot:	1	2	1	12		
Combined Completed Lots:	1	2	1	12		
Failures:	0	0	0	0		
Device on test:	31	63	23	380		
Mean Test Hour s/Device:	96	121	96	115		
Total Device Hours:	2,976	7,632	2,208	43,536		
Failure Analysis Number:						
				€`XILINX®		

Technology:	Si Gate CMOS
Device Type:	XC4XXXXV Microcircuit Group
Package Type:	BGA-560
Test Condition:	T = 121C; 2 atm. sat. steam

XC40125XV

XC4XXXXV

Period:	Oct. 1, 1998 to Oct. 1, 2000	
Combined Started Lot:	2	2
Combined Completed Lots:	2	2
Failures:	0	0
Device on test:	59	59
Mean Test Hour s/Device:	96	96
Total Device Hours:	5,664	5,664
Failure Analysis Number:		
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Technology:	Si Gate CMOS
Device Type:	XC4XXXXLA Microcircuit Group
Package Type:	BGA-560, HQFP-240,304, PQFP-240
Test Condition:	T = 121C; 2 atm. sat. steam

XC4013XLA XC4044XLA XC4062XLA XC4085XLA XC4XXXXLA

Period:		Oct. 1, 1998	to Oct. 1, 2000		
Combined Started Lot:	1	1	2	1	5
Combined Completed Lots:	1	1	2	1	5
Failures:	0	0	0	0	0
Device on test:	41	31	67	31	170
Mean Test Hour s/Device:	168	96	144	96	132
Total Device Hours:	6,888	2,976	9,672	2,976	22,512
Failure Analysis Number:					
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Technology:	Si Gate CMOS	
Device Type:	XCVXXX Microcircuit Group	
Package Type:	CS-144, FG-256, 556, 676, 680,	TQFP-144, HQFP-240
Test Condition:	T = 121C; 2 atm. sat. steam	

	XCV100	XCV200	XCV800	XCV1000	XCVXXX
Period:		Oct. 1, 19	98 to Oct. 1, 2000)	
Combined Started Lot:	2	3	3	2	10
Combined Completed Lots:	2	3	3	2	10
Failures:	0	0	0	0	0
Device on test:	122	148	116	53	439
Mean Test Hour s/Device:	168	133	96	126	132
Total Device Hours:	20,496	19,680	11,136	6,672	57,984
Failure Analysis Number:					
					—{ XILINX

Technology:	Si Gate CMOS
Device Type:	XCVXXXXE Microcircuit Group
Package Type:	BGA-560, 728, FG900, 1156
Test Condition:	T = 121C; 2 atm. sat. steam

	XCV1000E	XCV1600E	XCV2000E	XCVXXXXE
Period:	Oc	et. 1, 1998 to Oct. 1, 20	000	
Combined Started Lot:	2	1	3	6
Combined Completed Lots:	2	1	3	6
Failures:	0	0	0	0
Device on test:	61	22	59	142
Mean Test Hour s/Device:	168	168	123	149
Total Device Hours:	10,248	3,696	7,248	21,192
Failure Analysis Number:				
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Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined Technology: Si Gate CMOS Device Type: XC3XXX/A, XC31XX/A, XC4XXX, XCSXX/XL Package Type: Various Test Condition: T = -65C / +150C (Air to Air)					
	XC3XXX/A	XC31XX/A	XCSXX	XCSXXXXL	XC4XXX
Period:		Oct. 1, 1998	to Oct. 1, 2000		
Combined Started Lot:	2	1	1	18	2
Combined Completed Lots:	2	1	1	18	2
Failures:	0	0	0	0	0
Device on test:	152	45	45	818	121
Mean Test Cycles/Device:	1,026	1,004	1,005	999	1,010
Total Device Cycles:	155,952	45,180	45,225	817,544	122,244
Failure Analysis Number:					

Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined

Technology: Si Gate CMOS Device Type: XC4XXXE, XC4XXXEX, XC4XXXL, XC4XXXLA, XC4XXXV Package Type: Various Test Condition: T = -65C / +150C (Air to Air) T = -55C / +125C (Air to Air) for BGA,FG,CS

XC4XXXE XC4XXXEX XC4XXXXL XC4XXXXLA XC4XXXXV

Period:		Oct. 1, 1998	8 to Oct. 1, 2000		
Combined Started Lot:	8	4	19	12	3
Combined Completed Lots:	8	4	19	12	3
Failures:	0	0	1	0	0
Device on test:	349	179	679	552	95
Mean Test Cycles/Device:	1,046	885	980	979	1,010
Total Device Cycles:	365,097	158,350	665,704	540,191	95,968
Failure Analysis Number:					
				<u> </u>	(XILINX [®]
Technology:Si Gate CMOSDevice Type:XCVXXX, XCVXXXE, XC5XXXPackage Type:VariousTest Condition:T = -65C / +150C (Air to Air)T = -55C / +125C (Air to Air) for BGA,FG,CS

XCVXXX

XCVXXXE

XC5XXX

Period:	Oct. 1			
Combined Started Lot:	25	16	1	
Combined Completed Lots:	25	16	1	
Failures:	0	0	0	
Device on test:	808	464	45	
Mean Test Cycles/Device:	989	1,029	1,000	
Total Device Cycles:	799,484	477,286	45,000	
Failure Analysis Number:				
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Technology:	Si Gate CMOS
Device Type:	XC3XXX/A Microcircuit Group
Package Type:	PLCC- 68, VQFP-64
Test Condition:	T = -65C/+150C (Air to Air)

XC3030/A

XC3XXX/A

Period:	Oct. 1, 1998 to		
Combined Started Lot:	2	2	
Combined Completed Lots:	2	2	
Failures:	0	0	
Device on test:	152	152	
Mean Test Cycles/Device:	1,026	1,026	
Total Device Cycles:	155,592	155,592	
Failure Analysis Number:			
			──{{` XILINX [®]

Technology:	Si Gate CMOS
Device Type:	XC31XX/A Microcircuit Group
Package Type:	TQFP-176
Test Condition:	T = -65C/+150C (Air toAir)

XC3190/A

XC31XX/A

Period:	Oct. 1, 1998 to Oct. 1, 200	0	
Combined Started Lot:	1	1	
Combined Completed Lots:	1	1	
Failures:	0	0	
Device on test:	45	45	
Mean Test Cycles/Device:	1,004	1,004	
Total Device Cycles:	45,180	45,180	
Failure Analysis Number:			
		 \$`XILINX [®]	

Technology:	Si Gate CMOS
Device Type:	XCSXX Microcircuit Group
Package Type:	PQFP-240
Test Condition:	T = -65C/+150C (Air toAir)

XCS30

XCSXX

Period:	Oct. 1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	1
Combined Completed Lots:	1	1
Failures:	0	0
Device on test:	45	45
Mean Test Cycles/Device:	1,005	1,005
Total Device Cycles:	45,225	45,225
Failure Analysis Number:		
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Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined				
	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XCSXX Microcircu VQFP-100, PQFP-2 T = -65C/+150C (Air *For CS-280 T=-550	it Group 08, 240, CS-280 r toAir) C/+125C (Air to Air)	
	XCS30XL	XCS40XL*	XCS40XL	XCSXXXL
Period:	Oct.	1, 1998 to Oct. 1, 2000)	
Combined Started Lot:	6	1	11	18
Combined Completed Lots:	6	1	11	18
Failures:	0	0	0	0
Device on test:	270	41	507	818
Mean Test Cycles/Device:	952	1,000	1,025	999
	257,004	41,000	519,540	817,544
Total Device Cycles:				

Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined				
	Technolog Device Type Package Type Test Condition	 Si Gate CMOS XC4XXX Microcircuit (PQFP-160, BG-225 T = -65C/+150C (Air to *For BGA, T=-55C/+125 	Group Air) 5C (Air to Air)	
	XC4006	XC4013*	XC4XXX	
Period:	Oc	t. 1, 1998 to Oct. 1, 2000		
Combined Started Lot:	1	1	2	
Combined Completed Lots:	1	1	2	
Failures:	0	0	0	
Device on test:	45	76	121	
Mean Test Cycle/Device:	1,004	1,014	1,010	
Total Device Cycles:	45,180	77,064	122,244	
			{XILINX®	

Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined				
	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XC4XXXE Mi PQFP-208, 240 T = -65C/+1500	crocircuit Group), HQFP-240, PGA-223 C (Air to Air)	
	XC4010E	XC4013E	XC4025E	XC4XXXE
Period:	Oct.	1, 1998 to Oct. 1	, 2000	
Combined Started Lot:	1	6	1	8
Combined Completed Lots:	1	6	1	8
Failures:	0	0	0	0
Device on test:	80	193	76	349
Mean Test Cycles/Device:	748	1,182	1,014	1,046
Total Device Cycles:	59,815	228,218	77,064	365,097
				_\$*¥II INY®

Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined			
	Technology: Si Ga Device Type: XC42 Package Type: HQF Test Condition: T = -	ate CMOS XXXEX Microcircuit Group P-240 65C/+150C (Air to Air)	
	XC4028EX	XC4XXXEX	
Period:	Oct. 1, 1998	8 to Oct. 1, 2000	
Combined Started Lot:	4	4	
Combined Completed Lots:	4	4	
Failures:	0	0	
Device on test:	179	179	
Mean Test cycles/Device:	885	885	
Total Device Cycles:	158,350	158,350	
			— { _XILINX [®] —

Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined					
] Pa Tes	Technology: Device Type: ackage Type: st Condition:	Si Gate CMOS XC4XXXXL Microo HQFP-240, BGA-25 PQFP-,240, TQFP-1 T = -65C/+150C (Ai *For BGA, T=-55C/	circuit Group 56,352,432, 560, HT 76, PLCC-84 r to Air) +125C (Air to Air)	Ր-144
	XC4010XL	XC4013	XL XC4013XI	L* XC4020X	L XC4020XL*
Period:		Oct.	1, 1998 to Oct. 1, 2000		
Combined Started Lot:	2	1	1	1	2
Combined Completed Lots:	2	1	1	1	2
Failures:	0	0	0	0	0
Device on test:	152	45	45	45	44
Mean Test Cycles/Device:	1,040	1,006	1,060	1,094	1,000
Total Device cycles:	158,080	45,270	47,700	49,230	44,000
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	Reliability Tea Temperate Qualification	sting Summa ure Cycle (Ai n & Monitor	ry-Packages ir to Air) Combined	
	Techno Device Package Test Cond	blogy: Si Gate CM0 Fype: XC4XXXXL Fype: HQFP-240, PQFP-,240, 7 ition: T = -65C/+15 *For BGA, 7	DS Microcircuit Group BGA-256,352,432, 560, I FQFP-176, PLCC-84 50C (Air to Air) F=-55C/+125C (Air to Ai	HT-144 ir)
	XC4028XL	XC4036XL*	XC4052XL*	XC4062XL
Period:		Oct. 1, 1998 to Oct.	1, 2000	
Combined Started Lot:	2	3	1	1
Combined Completed Lots:	2	3	1	1
Failures:	0	0	0	1
Device on test:	85	32	32	45
Mean Test Cycles/Device:	1,000	1,020	1,000	1,005
Total Device cycles:	85,000	32,638	32,000	45,225
			F/A99036(1)-CRCP @1005 cy.
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	Reliability Testing Temperature Qualification &	g Summary-Pacl Cycle (Air to Air Monitor Combi	kages r) ned
	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XC4XXXXL Microcircu HQFP-240, BGA-256,35 PQFP-240, TQFP-176, P T = -65C/+150C (Air to *For BGA, T=-55C/+125	it Group 2,432, 560, HT-144 LCC-84 Air) C (Air to Air)
	XC4062XL*	XC4085XL*	XC4XXXXL
Period:	Oct.	1, 1998 to Oct. 1, 2000	
Combined Started Lot:	2	3	19
Combined Completed Lots:	2	3	19
Failures:	0	0	1
Device on test:	63	91	679
Mean Test Cycles/Device:	1,003	697	980
Total Device cycles:	63,176	63,385	665,704
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Technology:	Si Gate CMOS
Device Type:	XC4XXXXLA Microcircuit Group
Package Type:	HQFP-240, 304, PQFP-240, BG-256, 560
Test Condition:	T = -65C/+150C (Air to Air)
	*For BGA, T=-55C/+125C (Air to Air)

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	XC4013XLA	XC4020XLA*	XC4036XLA	XC4044XLA	XC4052XLA
Period:		Oct. 1, 199	8 to Oct. 1, 2000		
Combined Started Lot:	2	1	3	1	1
Combined Completed Lots:	2	1	3	1	1
Failures:	0	0	0	0	0
Device on test:	90	22	190	45	45
Mean Test Cycles/Device:	1,115	1,000	839	1,017	1,121
Total Device Cycles:	100,350	22,000	159,322	45,765	50,445

Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined				
	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XC4XXXXLA Mi HQFP-240, 304, P T = -65C/+150C (*For BGA, T=-55	crocircuit Group QFP-240, BG-256, 560 (Air to Air) C/+125C (Air to Air)	
	XC4062XLA	XC4085XLA	XC4085XLA*	XC4XXXXLA
Period:	Oct.	1, 1998 to Oct. 1, 20	00	
Combined Started Lot:	2	1	1	12
Combined Completed Lots:	2	1	1	12
Failures:	0	0	0	0
Device on test:	75	41	44	552
Mean Test Cycles/Device:	1,008	1,000	1,000	979
Total Device Cycles:	75,587	42,722	44,000	540,191

	Reliability Testing Temperature (Qualification & 2	g Summary-Pa Cycle (Air to A Monitor Comb	ckages ir) oined	
	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XC4XXXXV Microcir BGA-560 T = -65C/+150C (Air t *For BGA, T=-55C/+1	cuit Group to Air) 25C (Air to Air)	
	XC40150XV	XC40125XV*	XC4XXXX	V
Period:	Oct. 2	1, 1998 to Oct. 1, 2000		
Combined Started Lot:	1	2	3	
Combined Completed Lots:	1	2	3	
Failures:	0	0	0	
Device on test:	30	65	95	
Mean Test Cycles/Device:	1,000	1,015	1,010	
Total Device Cycles:	30,000	65,968	95,968	

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	Reliability Testing Temperature Qualification &	g Summary-Pack Cycle (Air to Air Monitor Combin	kages ·) ned
	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XCVXXX Microcircuit G HQFP-240, CS-,144, TQ FG-256,456,556,676,680, T = -65C/+150C (Air to A *For CS, BGA,FG, T=-5	Group FP-144, PQFP-240 BGA-432-560 Air) 5C/+125C (Air to Air)
	XCV50	XCV100*	XCV100
Period:	Oct.	1, 1998 to Oct. 1, 2000	
Combined Started Lot:	2	1	2
Combined Completed Lots:	2	1	2
Failures:	0	0	0
Device on test:	49	62	88
Mean Test Cycles/Device:	1,096	1,085	1,033
Total Device Cycles:	53,710	67,270	90,892
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	Reliability To Tempera Qualificatio	esting Summa ture Cycle (Air on & Monitor (ry-Packages r to Air) Combined	
	Tech Devic Packag Test Co	anology:Si Gate CMOare Type:XCVXXX Midbe Type:HQFP-240, CFG-256,456,55FG-256,456,55ndition: $T = -65C/+150$ *For CS, BGA	S crocircuit Group 'S-,144, TQFP-144, PQF 56,676,680, BGA-432-560 OC (Air to Air) A,FG, T=-55C/+125C (Ai	P-240 ar to Air)
	XCV200	XCV300	XCV300*	XCV600
Period:		Oct. 1, 1998 to Oct. 1	1, 2000	
Combined Started Lot:	4	4	2	1
Combined Completed Lots:	4	4	2	1
Failures:	0	0	0	0
Device on test:	138	151	44	22
Mean Test Cycles/Device:	1,010	877	1,028	1,036
Total Device Cycles:	139,342	132,376	45,232	22,792
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	Reliability ' Temper Qualificat	Festing Su ature Cyc tion & Mo	Immary-Packages le (Air to Air) nitor Combined	
	To De Pack Test o	echnology: Si G vice Type: XCV xage Type: HQI FG- Condition: T = *For	ate CMOS VXXX Microcircuit Group FP-240, CS-,144, TQFP-144, H 256,456,556,676,680, BGA-432 -65C/+150C (Air to Air) r CS, BGA,FG, T=-55C/+1250	PQFP-240 2-560 C (Air to Air)
	XCV800	XCV800	* XCV1000*	XCVXXX
Period:		Oct. 1, 199	28 to Oct. 1, 2000	
Combined Started Lot:	3	2	3	25
Combined Completed Lots:	3	2	3	25
Failures:	0	0	0	0
Device on test:	50	94	78	808
Mean Test Cycles/Device:	1,000	895	1,010	989
Total Device Cycles:	50,000	84,078	78,792	799,484
				──{` XILINX [®] ──

	Reliab Ter Qual	ility Testing mperature (ification & 1	s Summ Cycle (A Monito	ary-Packages Air to Air) or Combined	
		Technology: Device Type: Package Type: Test Condition:	Si Gate CI XCVXXX HQFP-240 BGA-560, T = -65C/4 *For FG,E	MOS E Microcircuit Group), PQFP-240, FG456,900,1 728, CS-144 -150C (Air to Air) 8GA, CS, T=-55C/+125C	1156, (Air to Air)
	XCV200E	XCV3	00E	XCV300E*	XCV1600E
Period:		Oct. 2	1, 1998 to O	ct. 1, 2000	
Combined Started Lot:	1		2	2	1
Combined Completed Lots:	1		2	2	1
Failures:	0)	0	0
Device on test:	74	14	l	20	22
Mean Test Cycles/Device:	1,000	1,057	7	1,023	1,000
Total Device Cycles:	74,000	149,103	3	20,464	22,000
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	Reliability T Tempera Qualificati	Cesting Summa ature Cycle (A ion & Monitor	ary-Packages ir to Air) c Combined	
	Teo Dev Packa Test C	chnology: Si Gate CM ice Type: XCVXXXE nge Type: HQFP-240, BGA-560, 7 ondition: T = -65C/+1 *For FG,BC	OS Microcircuit Group PQFP-240, FG456,900 28, CS-144 50C (Air to Air) GA, CS, T=-55C/+1250	9,1156, C (Air to Air)
	XCV1000E	XCV1000E*	XCV2000E*	XCVXXXE
Period:		Oct. 1, 1998 to Oct	t. 1, 2000	
Combined Started Lot:	1	3	5	16
Combined Completed Lots:	1	3	5	16
Failures:	0	0	0	0
Device on test:	24	77	84	464
Mean Test Cycles/Device:	1,084	1,124	919	1,029

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Technology:	Si Gate CMOS
Device Type:	XC5XXX Microcircuit Group
Package Type:	VQFP-100
Test Condition:	T = -65C/+150C (Air to Air)

XC5202

XC5XXX

Period:		Oct. 1, 1998 to Oct. 1, 2000	
Combined Started Late	1	1	
Compined Started Lot:	1	1	
Combined Completed Lots:	1	1	
Failures:	0	0	
Device on test:	45	45	
Mean Test Cycles/Device:	1,000	1,000	
Total Device Cycles:	45,000	45,000	
Failure Analysis Number:			
			<u> </u>

	Reliabi Quali	lity Testing H fication & N Technology: Device Type: Package Type: Test Condition:	Summ ast /Ionito Si Gate CI XC3XXX, Various T = 130C,	ary-Packages or Combined Mos XC4XXX/E, XC4XXXXLA R.H. = 85%	Microcircuit Group
		Bias Voltage:	5.0V +/2	5V, 3.3V+/25V, 2.7V+/25V	V
	XC3XXX	XC4XX	XXE	XC4XXXL	XC4XXXXLA
Period:		Oct. 1,	1998 to O	ct. 1, 2000	
Combined Started Lot:	1		3	1	2
Combined Completed Lots:	1		3	1	2
Failures:	0		0	0	0
Device on test:	36	4	45	12	36
Mean Test Hours/Device:	300	12	27	300	200
Total Device Hours:	10,800	5,70)0	3,600	7,200
0 / 1 2000 P02					_ {` XILINX®

	Reliability 7 Qualificat To De Pack	Festing Summ Hast ion & Monito echnology: Si Gate CN vice Type: XC4XXXX Microcircu tage Type: Various	ary-Packages r Combined 105 xv,xcvxxx, xcsxxxI uit Group	L, XCVXXXE
	Test (Bia	Condition: $T = 130C$, 1 as Voltage: 5.0V +/25	R.H. = 85% 5V, 3.3V+/25V, 2.7V+/	.25V
	XC4XXXXV	XCVXXX	XCSXXXL	XCVXXXE
Period:		Oct. 1, 1998 to Oc	et. 1, 2000	
Combined Started Lot:	1	11	2	7
Combined Completed Lots:	1	11	2	7
Failures:	0	0	0	0
Device on test:	12	196	49	207
Mean Test Hours/Device:	300	172	129	100
Total Device Hours:	3,600	33,700	6,300	20,742
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	Reliability Testing I Qualification & Technology: Device Type: Package Type: Test Condition: Bias Voltage:	g Summary-Packages Hast Monitor Combined Si Gate CMOS XC3XXX Microcircuit Group PLCC-68 T = 130C, R.H. = 85% 5.0V +/25V	
	XC3030/A	XC3	SXXX
Period:	Oct.	1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	1	
Combined Completed Lots:	1	1	
Failures:	0	0	
Device on test:	36	36	
Mean Test Hours/Device:	300	300	
Total Device Hours:	10,800	10,800	
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Reliability Testing Summary-Packages Hast Qualification & Monitor Combined				
	Technology: Device Type: Package Type: Test Condition: Bias Voltage:	Si Gate CMOS XC4XXXE Microcircuit Group PQFP-240, HQFP-240 T = 130C, R.H. = 85% 5.0V +/25V		
	XC4013E	XC4025E	XC4XXXE	
Period:	Oct.	1, 1998 to Oct. 1, 2000		
Combined Started Lot:	1	2	3	
Combined Completed Lots:	1	2	3	
Failures:	0	0	0	
Device on test:	22	23	45	
Mean Test Hours/Device:	100	152	127	
Total Device Hours:	2,200	3,500	5,700	

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Reliability Testing Summary-Packages Hast Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XC4XXXL Microcircuit Group
Package Type:	PQFP-208
Test Condition:	T = 130C, R.H. = 85%
Bias Voltage:	3.3V +/25V

XC4020XL

XC4XXXL

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Period:	Oct. 1, 1998 to Oct. 1, 2000		
Combined Started Lot:	1	1	
Combined Completed Lots:	1	1	
Failures:	0	0	
Device on test:	12	12	
Mean Test Hours/Device:	300	300	
Total Device Hours:	3,600	3,600	

Reliability Testing Summary-Packages Hast Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XC4XXXXLA Microcircuit Group
Package Type:	HQFP-240
Test Condition:	T = 130C, R.H. = 85%, 3ATM
Bias Voltage:	3.3V +/25V

XC4036XLA

XC4XXXXLA

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Period:	Oct. 1, 1998 to Oct. 1, 200	00
Combined Started Lot:	2	2
Combined Completed Lots:	2	2
Failures:	0	0
Device on test:	36	36
Mean Test Hours/Device:	200	200
Total Device Hours:	7,200	7,200

Reliability Testing Summary-Packages Hast Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XC4XXXXV Microcircuit Group
Package Type:	HQFP-240
Test Condition:	T = 130C, R.H. = 85%, 3ATM
Bias Voltage:	2.7V +/25V

XC40150XV

XC4XXXXV

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Period:	Oct. 1, 1	998 to Oct. 1, 2000	
Combined Started Lot:	1	1	
Combined Completed Lots:	1	1	
Failures:	0	0	
Device on test:	12	12	
Mean Test Hours/Device:	300	300	
Total Device Hours:	3,600	3,600	

	Reliabilit Qualific	y Testing S Ha cation & M	Summary-Pa ist Ionitor Coml	ckages Dined	
	Technology:Si Gate CMOSDevice Type:XCVXXX Microcircuit GroupPackage Type:PQFP-240, HQFP-240, FG-256,556, BGA-560Test Condition:T = 130C, R.H. = 85%Bias Voltage:2.7V +/25V				
	XCV200	XCV300	XCV800	XCV1000	XCVXXX
Period:	Oct. 1, 1998 to Oct. 1, 2000				
Combined Started Lot:	2	3	3	3	11
Combined Completed Lots:	2	3	3	3	11
Failures:	0	0	0	0	0
Device on test:	42	71	59	24	196
Mean Test Hours/Device:	150	168	175	217	172
Total Device Hours:	6,300	11,900	10,300	5,200	33,700

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Reliability Testing Summary-Packages Hast Qualification & Monitor Combined					
	Technology: Device Type: Package Type: Test Condition: Bias Voltage:	Si Gate CMOS XCSXXXL Microcircuit Group CS-280 T = 130C, R.H. = 85%, 3ATM 3.3V +/3V			
	XCS40XL	XCSXXXL			
Period:	Oct.	Oct. 1, 1998 to Oct. 1, 2000			
Combined Started Lot:	2	2			
Combined Completed Lots:	2	2			
Failures:	0	0			
Device on test:	49	49			
Mean Test Hours/Device:	129	129			
Total Device Hours:	6,300	6,300			

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Reliability Testing Summary-Packages Hast Qualification & Monitor Combined				
	Technology: Device Type: Package Type: Test Condition: Bias Voltage:	Si Gate CMOS XCVXXXE Microcircuit Group BGA-560,728, FG900, 1156, PQFP-2 T = 130C, R.H. = 85% 1.9V +/1V	40	
	XCV300E	XCV1000E	XCV1600E	
Period:	Oct.	1, 1998 to Oct. 1, 2000		
Combined Started Lot:	1	2	1	
Combined Completed Lots:	1	2	1	
Failures:	0	0	0	
Device on test:	76	43	22	
Mean Test Hours/Device:	100	101	100	
Total Device Hours:	7,600	4,342	2,200	
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Reliability Testing Summary-Packages Hast Qualification & Monitor Combined				
	Technology: Device Type: Package Type: Test Condition: Bias Voltage:	Si Gate CMOS XCVXXXE Microcircuit Group BGA-560,728, FG900, 1156, PQFP-240 T = 130C, R.H. = 85% 1.9V +/1V	0	
	XCV2000E	XCV812E	XCVXXXE	
Period:	Oct.	1, 1998 to Oct. 1, 2000		
Combined Started Lot:	2	1	7	
Combined Completed Lots:	2	1	7	
Failures:	0	0	0	
Device on test:	44	22	207	
Mean Test Hours/Device:	100	100	100	
Total Device Hours:	4,400	2,200	20,742	
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The Coolrunner Products



Reliability Testing Summary High Temperature Life Test Qualification & Monitor Combined

Technology:Si Gate CMOSDevice Type:XCR3960Package Type:BG492Actual Temperature:125CActual Voltage:3.6VAssumed Activation Energy:0.7 ev @ C.L. = 60%

XCR3960

Combined Lots:	3
Failures:	2
Device on test:	_ 198
Actual device hours:	198,000
Mean :	1.000
Equivalent device hours @ Tj=70C:	5.209.747
Equivalent device hours @ Tj=55C:	15,372,654
Equivalent device hours @ Tj=25C:	1.86E+08
Failure Rate (60% C.L.) in FITS @ Tj=70C:	594
Failure Rate (60% C.L.) in FITS @ Tj=55C:	201
Failure Rate (60% C.L.) in FITS @ Tj=25C:	17

Failure Analysis:

F/A(2)-Std by current

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Reliability Testing Summary High Temperature Life Test Qualification & Monitor Combined

Technology: Si Gate CMOS Device Type: XCR5064, XCR3(5)128, XCR22(L)V10, XCR3(5)032 Package Type: PLCC44, 84, 28 Actual Temperature: 150C Actual Voltage: 3.6V & 5.5V Assumed Activation Energy: 0.7 ev @ C.L. = 60%

XCR5064 XCR3(5)128 XCR22(L)V10 XCR3(5)032 XCRXXXX

Combined Lots:	2	2	1	4	9
Failures:	1	2	0	0	3
Device on test:	150	172	154	306	782
Actual device hours:	149,168	133,072	154,000	306,000	779,726
Mean :	994	774	1,000	1,000	997
Equivalent device hours @ Tj=70C:	16,393,549	11,687,534	13,525,612	26,875,566	68,482,280
Equivalent device hours @ Tj=55C:	48,373,242	34,486,974	39,910,680	79,303,039	202,073,992
Equivalent device hours @ Tj=25C:	5.84E+08	4.16E+08	4.82E+08	9.57E+08	2.44E+09

 Failure Analysis:
 F/A(1)-Gate oxide defect

ct F/A(2)-1-Idd failure, 1-single bit charge loss

- Failure Rate (60% C.L.) in FITS @ Tj=70C: 61
- Failure Rate (60% C.L.) in FITS @ Tj=55C: 35
- Failure Rate (60% C.L.) in FITS @ Tj=25C: 3

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Reliability Testing Summary High Temperature Life Test Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XCR3XXXXL
Package Type:	TQ144
Actual Temperature:	145C
Actual Voltage:	3.6V
Assumed Activation Energy:	0.7 ev @ C.L. = 60%

Combined Lots:	1	1	1	3	
Failures:	1	0	0	5 1	
Device on test:	78	77	78	233	
Actual device hours:	78,732	121,680	82,524	282,936	
Mean :	1,009	1,560	1,058	1,209	
Equivalent device hours @ Tj=70C:	5,508,357	8,513,144	5,773,658	19,795,158	
Equivalent device hours @ Tj=55C:	16,264,439	25,136,628	17,047,790	58,448,857	
Equivalent device hours @ Tj=25C:	1.96E+08	3.04E+08	2.06E+08	7.07E+08	

Failure Analysis: F/A00001(1)-INC

Failure Rate (60% C.L.) in FITS @ Ti=70C:	102
Failure Rate (60% C.L.) in FITS @ Tj=55C:	35
Failure Rate (60% C.L.) in FITS @ Tj=25C:	3

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XCR3256XL XCR3064XL XCR3128XL XCR3XXXXL

F	Reliability Tes Qualification Techno Device Package Test Cond Bias Vol	ting Summary- Hast & Monitor Co Nogy: Si Gate CMOS Type: XCR3960, XCR3(Type: BGA492, PC84, C ition: T = 130C, R.H. = 3 Itage: 3.6V, 5.5V	Packages mbined 5)128, XCR3064A P56 85%,		
	XCR3960	XCR3(5)128	XCR3064A	XCRXXX	
Combined Started Lot:	3	1	1	3	
Combined Completed Lots:	3	1	1	3	
Failures:	0	1	0	1	
Device on test:	105	77	44	226	
Mean Test Hours/Device:	96	96	100	97	
Total Device Hours:	10,080	7,392	4,400	21,872	
Failure Analysis:	Failure Analysis: 1F- single bit charge loss				
				_\$ TXILINX≗	
Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined					
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	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XCR3960, XCR5064, XCR3(5) BGA-492, TQ-44, LQ-128, TQ TQFP-100, CP-56, PC-28 T = -55C/+125C (Air to Air) T= -65C/+150C (Air to Air))128, XCR22(L)V10 9100, PLCC-44,84, PQFP-100		
	XCR3960	XCR5064	XCR3(5)128		
Combined Started Lot:	3	2	7		
Combined Completed Lots:	3	2	7		
Failures:	0	0	1		
Device on test:	89	154	614		
Mean Test Cycles/Device:	1,000	1,000	475		
Total Device Cycles:	89,000	154,000	291,600		
Failure Analysis:		F/A(1)-S	ingle bit charge loss		

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Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined				
	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XCR3960, XCR5064, X BGA-492, TQ-44, LQ-1 TQFP-100, CP-56, PC-2 T = -55C/+125C (Air to T= -65C/+150C (Air to	CR3(5)128, XCR22(L)V10 28, TQ100, PLCC-44,84, PQFP-100 28 9 Air) Air)	
	XCR3(5)064	XCR22(L)V10	XCRXXXX	
	4	1	17	
Combined Started Lot:	4	1		
Combined Completed Lots:	4	1	1/	
Failures:	0	0	0	
Device on test:	301	152	1,310	
Mean Test Cycles/Device:	1,000	500	696	
Total Device Cycles:	301,000	76,000	911,600	
Failure Analysis:				
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Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XCR3256XL, XCR3128XL
Package Type:	TQ144, CS-144
Test Condition:	T = -65C/+150C (Air to Air)
	T = -55C/+125C (Air to Air)

	XCR3256XL	XCR3128XL	XCRXXXXXL	
Combined Started Lot:	1	1	1	
Combined Completed Lots:	1	1	1	
Failures:	0	0	0	
Device on test:	74	76	74	
Mean Test Cycles/Device:	1,060	1,000	1,060	
Total Device Cycles:	78,440	76,000	78,440	
Failure Analysis:				

• **{ `** XILINX [®]

Technology:	Si Gate CMOS
Device Type:	XCR3960,5064,3(5)128,3(5)032
Package Type:	BGA492, TQ44, PC44,84, PQ100, TQ100, LQ128, CP56
Test Condition:	T = 121C; 15 PSIG (unbiased)

= **{ `**XILINX®

	XCR3960	XCR3(5)064	XCR3(5)128	XCR3(5)032	XCRXXXX	
Combined Started Lot:	3	7	7	3	20	
Combined Completed Lots:	3	7	7	3	20	
Failures:	4	0	0	0	0	
Device on test:	101	533	607	231	1,472	
Mean Test Hour s/Device:	166	217	123	168	167	
Total Device Hours:	16,752	115,584	74,760	38,808	245,904	
Failure Analysis Number: F/A(.	3)2-pkg warp					

2-Stdby current

Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XCR3(5)032 Microcircuit Group
Package Type:	PC44
Test Condition:	T = 85C, R.H. = 85%
Bias Voltages:	3.0V & 5.0V

XC3(5)032

-{{`XILINX[®]

Combined Started Lot:	3	
Combined Completed Lots:	3	
Failures:	0	
Device on test:	230	
Mean Test Hour s/Device:	1,000	
Total Device Hours:	230,000	
Failure Analysis Number:		

Reliability Testing Summary-Packages Erase Cycling Qualification & Monitor Combined

Technology: Si Gate CMOS Device Type: XCR3(5)128 Package Type: PLCC- 84 Test Condition: 25C Voltage: Vcc=5.0V, Vpp=12.0-12.5V

XCR3(5)128

EXILINX[®]

1	Combined Started Lot:
1	Combined Completed Lots:
0	Failures:
10	Device on test:
1,000	Mean Test Cycles/Device:
10,000	Total Device Cycles:

The CPLD & EPROM Products



Technology:	Si Gate CMOS
Device Type:	XC17XXXD, XC17XXXE, XC17XXXI
Package Type:	Various
Actual Temperature:	145C
Actual Voltage:	5.7V +/-0.25, 3.3V+/-0.3V
Assumed Activation Energy:	0.58 ev for Eprom

XC17XXXD

XC17XXXE

Oct. 1, 1998 to Oct. 1, 2000

XC17XXL

EXILINX®

Combined Lots:	2	4	8
Failures:	0	0	1
Device on test:	123	365	519
Actual device hours:	127,704	332,700	715,912
Mean :	1,038	912	1,379
Equivalent device hours @ Tj=125C:	286,749	747,052	1,607,525
Equivalent device hours @ Tj=55C:	10,578,403	27,559,315	59,302,809
Equivalent device hours @ Tj=25C:	8.34E+07	2.17E+08	4.68E+08
Failure Rate (60% C.L.) in FITS @ Tj=55C:	87	33	34
Failure Rate (60% C.L.) in FITS @ Tj=25C:	11	4	4

Failure Analysis:

Period:

Technology: Si Gate CMOS Device Type: XC17SXX/XL, XC17XXXXL Package Type: Various Actual Temperature: 145C Actual Voltage: 5.7V +/-0.25, 3.3V+/-0.3V Assumed Activation Energy: 0.58 ev for Eprom;

XC17SXX

XC17SXXXL

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Period:	Oct. 1, 199	8 to Oct. 1, 2000
Combined Lots:	10	5
Failures:	1	1
Device on test:	759	411
Actual device hours:	852,166	531,299
Mean :	1,123	1,293
Equivalent device hours @ Tj=125C:	1,913,472	1,192,991
Equivalent device hours @ Tj=55C:	70,589,454	44,010,329
Equivalent device hours @ Tj=25C:	5.59E+08	3.47E+08
Failure Rate (60% C.L.) in FITS @ Tj=55C:	29	46
Failure Rate (60% C.L.) in FITS @ Tj=25C:	4	6

Failure Analysis:

Technology:Si Gate CMOSDevice Type:XC18XX, XC95XXX, XC95XXXLPackage Type:VariousActual Temperature:145CActual Voltage:5.7V +/-0.25, 3.3V+/-0.3VAssumed Activation Energy:0.58 ev for Eprom; 0.7 e.v. for XC95XXX

XC18XX

XC95XXX

XC95XXXXL

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Period	:

Oct. 1, 1998 to Oct. 1, 2000

Combined Lots:	2	16	6
Failures:	0	0	0
Device on test:	136	923	454
Actual device hours:	218,320	744,261	523,237
Mean :	1,605	806	1,153
Equivalent device hours @ Tj=125C:	490,221	1,975,630	1,388,925
Equivalent device hours @ Tj=55C:	18,084,610	153,749,726	18,090,186
Equivalent device hours @ Tj=25C:	1.43E+08	1.86E+09	1.31E+09
Failure Rate (60% C.L.) in FITS @ Tj=55C:	51	6	8
Failure Rate (60% C.L.) in FITS @ Tj=25C:	6	0.5	0.7

Failure Analysis:

Technology:Si Gate CMOSDevice Type:XC17XXXD Microcircuit GroupPackage Type:DD8, PLCC-20Actual Temperature:145C +8C/-0CActual Voltage:5.7V +/-0.25VAssumed Activation Energy:0.58 ev @ C.L. = 60%

XC17256D

XC17XXXD

Period:	Oct. 1, 1998 to Oct. 1, 2000		
Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C:	2 0 123 127,704 1,038 286,749 10,578,403	2 0 123 127,704 1,038 286,749 10,578,403	
Equivalent device hours @ 1j=25C: Failure Analysis:	8.34E+07 Failure Rate (60% C.L.) in FITS @ Tj=55C: Failure Rate (60% C.L.) in FITS @ Tj=25C:	8.34E+07 87 11	
	х, , , , , , , , , , , , , , , , , , ,	── { XILINX [®]	

Technology:	Si Gate CMOS
Device Type:	XC17XXL Microcircuit Group
Package Type:	PD8, VQFP-44, CC-44
Actual Temperature:	145C +8C/-0C
Actual Voltage:	3.3V +/-0.3V
Assumed Activation Energy:	0.58 ev @ C.L. = 60%

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XC1704L

XC17XXL

Period:	Oct. 1, 199	98 to Oct. 1, 2000	
Combined Lots:	6	2	8
Failures:	1	0	1
Device on test:	365	154	519
Actual device hours:	522,000	193,912	715,912
Mean :	1,430	1,259	1,379
Equivalent device hours @ Tj=125C:	1,172,110	435,414	1,607,525
Equivalent device hours @ Tj=55C:	43,240,044	16,062,765	59,302,809
Equivalent device hours @ Tj=25C:	3.41E+08	1.27E+08	4.68E+08
Failure Analysis:	F/A 99111(1)-FANC		
	Failure Rate (60% C.L.)	in FITS @ Tj=55C:	34
	Failure Rate (60% C.L.)	in FITS @ Tj=25C:	4
			{XILINX ®

(Reliabil High Te Qualificatio	ity Testing mperature on & Moni	Summary Life Test tor Combin	t I ed	
As	Tech Devic Packag Actual Tempo Actual V Sumed Activation	inology: Si Gate e Type: XC17S ge Type: PD8, C erature: 145C + Voltage: * 3.3V 5.7+/-0. Energy: 0.58 ev	CMOS XX Microcircuit G C44 8C/-0C +/-0.3V, .25V @ C.L. = 60%	roup	
		XC17820	X C17830	XC17S40*	XC17SXX
	XC17805	AC17520	A C17550	AC17540	
Period:	XC17805	Oct. 1, 1998 to ()ct. 1, 2000	AC17540	
Period: Combined Lots:	1 1	AC17520 Oct. 1, 1998 to (1	A C17550	5	10 10
Period: Combined Lots: Failures: Device on test:	XCI7S05	AC17520 Oct. 1, 1998 to (1 0	Ct. 1, 2000	5 1	10 1 750
Period: Combined Lots: Failures: Device on test: Actual device hours:	1 0 106	AC17520 Oct. 1, 1998 to (1 0 106	A C17550	5 1 289	10 1 759 852 166
Period: Combined Lots: Failures: Device on test: Actual device hours: Mean :	XCT/S05	AC17520 Oct. 1, 1998 to (1 0 106 108,438 1 023	A C17550 Det. 1, 2000 3 0 258 265,290 1 028	5 1 289 370,000 1 280	10 1 759 852,166 1 123
Period: Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Ti=125C:	1 0 106 108,438 1,023 243,489	AC17520 Oct. 1, 1998 to (1 0 106 108,438 1,023 243 489	A C17550 Dct. 1, 2000 3 0 258 265,290 1,028 595 688	5 1 289 370,000 1,280 830 806	10 1 759 852,166 1,123 1 913 472
Period: Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C:	1 0 106 108,438 1,023 243,489 8 982 498	AC17520 Oct. 1, 1998 to (1 0 106 108,438 1,023 243,489 8 982 498	A C17530 Det. 1, 2000 3 0 258 265,290 1,028 595,688 21 975 385	5 1 289 370,000 1,280 830,806 30 649 073	10 1 759 852,166 1,123 1,913,472 70,589,454
Period: Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C:	1 0 106 108,438 1,023 243,489 8,982,498 7.08E+07	AC17320 Oct. 1, 1998 to (1 0 106 108,438 1,023 243,489 8,982,498 7.08E+07	A C17530 Dct. 1, 2000 3 0 258 265,290 1,028 595,688 21,975,385 1.73E+08	5 1 289 370,000 1,280 830,806 30,649,073 2.42E+08	10 1 759 852,166 1,123 1,913,472 70,589,454 5.57E+08
Period: Combined Lots: Failures: Device on test: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C: Failure Analysis:	1 0 106 108,438 1,023 243,489 8,982,498 7.08E+07	AC17320 Oct. 1, 1998 to (1 0 106 108,438 1,023 243,489 8,982,498 7.08E+07	A C17530 Det. 1, 2000 3 0 258 265,290 1,028 595,688 21,975,385 1.73E+08	5 1 289 370,000 1,280 830,806 30,649,073 2.42E+08 F/A99111(1)-FANC	10 1 759 852,166 1,123 1,913,472 70,589,454 5.57E+08

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Technology:Si Gate CMOSDevice Type:XC17SXL Microcircuit GroupPackage Type:PD8Actual Temperature:145C +8C/-0CActual Voltage:3.3V +/-0.3VAssumed Activation Energy:0.58 ev @ C.L. = 60%

XC17S10XL

XC17S40XL

XC17S150XL X

XC17SXXXL

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Period:	(Oct. 1, 1998 to Oct. 1, 2	2000	
Combined Started Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Ti=25C:	1 0 107 109,140 1,020 245,0665 9,040,648 7.13E+07	1 0 107 109,461 1,023 245,786 9,067,238 7,15E+07	3 1 197 312,698 1,587 702,139 25,902,443 2.04E+08	5 1 411 531,299 1,293 1,192,991 44,010,329 3.47E+08
Failure Analysis:			F/A 99111(1)-FANC	
		Failure R Failure R	ate (60% C.L.) in FITS ate (60% C.L.) in FITS	@ Tj=55C: 46 @ Tj=25C: 6

Technology:Si Gate CMOSDevice Type:XC17XXXE Microcircuit GroupPackage Type:PD8Actual Temperature:145C +8C/-0CActual Voltage:5.7V +/-0.25VAssumed Activation Energy:0.58 ev @ C.L. = 60%

XC17256E

XC17XXXE

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Period:	Oct. 1, 1998 to Oct. 1, 2000	
Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=25C: Equivalent device hours @ Tj=25C:	4 0 365 332,700 912 747,052 27,559,315 2.17E+08	4 0 365 332,700 912 747,052 27,559,315 2.17E+08
Failure Analysis: Failure Ra Failure Ra	nte (60% C.L.) in FITS @ Tj=55C: nte (60% C.L.) in FITS @ Tj=25C:	33 7

Technology:Si Gate CMOSDevice Type:XC18VXX Microcircuit GroupPackage Type:VQF-44Actual Temperature:145C +8C/-0CActual Voltage:3.3V +/-0.3VAssumed Activation Energy:0.58 ev @ C.L. = 60%

XC18V04

XC18VXX

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Period:	Oct. 1, 1998 to Oct. 1, 2000	
Combined Lots:	2	2
Failures:	0	0
Device on test:	136	136
Actual device hours:	218,320	218,320
Mean :	1,605	1,605
Equivalent device hours @ Tj=125C:	490,221	490,221
Equivalent device hours @ Tj=55C:	18,084,610	18,084,610
Equivalent device hours @ Tj=25C:	1.43E+08	1.43E+08
Failure Rate (60	9% C.L.) in FITS @ Tj=55C:	51
Failure Rate (60	9% C.L.) in FITS @ Tj=25C:	6

Reliability Testing Summary High Temperature Operating Life Qualification & Monitor

Si Gate CMOS
XC95XXX Microcircuit Group
PLCC-44 & 84 & PQFP-160, HQFP-208
145C +8C/-0C
5.7V +/-0.25V
0.7 ev @ C.L. = 60%

XC95108

XC95144

XC9536

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Period:	Oct. 1, 1998	to Oct. 1, 2000	
Combined Lots:	3	2	6
Failures:	0	0	0
Device on test:	147	126	334
Actual device hours:	89,127	133,473	267,150
Mean :	606	1,059	800
Equivalent device hours @ Tj=125C:	236,586	354,302	709,146
Equivalent device hours @ Tj=55C:	18,411,836	27,572,823	55,187,789
Equivalent device hours @ Tj=25C:	2.23E+08	3.33E+08	6.67E+08

Failure Analysis:

Reliability Testing Summary High Temperature Operating Life Qualification & Monitor

Si Gate CMOS
XC95XXX Microcircuit Group
PLCC-44 & 84 & PQFP-160, HQFP-208
145C +8C/-0C
5.7V +/-0.25V
0.7 ev @ C.L. = 60%

XC9572

XC95216

XC95XXX

XC95288

Period:		Oct. 1, 1998 to Oct. 1	1, 2000	
Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C: Failure Analysis:	2 0 120 86,685 722 230,104 17,907,368 2.17E+08	2 0 120 90,990 758 241,532 18,796,694 2.27E+08	1 0 76 76,836 1,011 203,960 15,872,764 1.92E+08	16 0 923 744,261 806 1,975,630 153,749,276 1.86E+09
	Failure Failure	Rate (60% C.L.) in F Rate (60% C.L.) in F	TITS @ Tj=55C: TITS @ Tj=25C:	6 0.5
Oct. 1. 2000 P126				

Reliability Testing Summary High Temperature Operating Life Qualification & Monitor

Technology:	Si Gate CMOS
Device Type:	XC95XXXL Microcircuit Group
Package Type:	PQFP-160, 208, HQFP-208, PLCC-44
Actual Temperature:	145C +8C/-0C
Actual Voltage:	3.3V +/-0.3V
Assumed Activation Energy:	0.7 ev @ C.L. = 60%

XC9536XL

XC95144XL

XC95288XL

XC95XXXL

Period:		Oct. 1, 1998 to Oct.	1, 2000	
Combined Lots: Failures: Device on test: Actual device hours: Mean : Equivalent device hours @ Tj=125C: Equivalent device hours @ Tj=55C: Equivalent device hours @ Tj=25C:	1 0 76 233,016 3,066 618,538 48,136,395 5.82E+08	2 0 151 111,253 737 295,319 22,982,621 2.78E+08	3 0 227 178,968 788 475,068 36,971,171 4.47E+08	6 0 454 523,237 1,153 1,388,925 18,090,186 1.31E+09
Failure Analysis:				
Failure R Failure R	ate (60% C.L.) in H ate (60% C.L.) in H	FITS @ Tj=55C: FITS @ Tj=25C:		8 0.7
				—{ ∑XILINX [®]

	Reliability Testing Bias Mo Qualification & I	s Summary-Packa Sisture Life Monitor Combine	ges d
	Technology: Device Type: Package Type: Test Condition: Bias Voltages:	Si Gate CMOS XC17XX/L, XC17SXX, XC1 T=85C, R.H.=85% 5.0V +/25V	7XXXE
	XC17XX/L	XC17SXX	XC17XXE
Period:	Oct. 1	1, 1998 to Oct. 1, 2000	
Combined Started Lot:	2	3	1
Combined Completed Lots:	2	3	1
Failures:	0	0	0
Device on test:	121	135	45
Mean Test Hour s/Device:	1,074	1,048	1,004
Total Device Hours:	129,913	141,525	45,180

Oct. 1, 2000 P128

Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XC18VXX, XC95XXX, XC95XXXXL
Package Type:	Various
Test Condition:	T=85C, R.H.=85%
Bias Voltages:	5.0V +/25V, 3.3V +/3V

XC18VXX

XC95XXX

XC95XXXXL

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Period:		Oct. 1, 1998 to Oct. 1, 2000		
Combined Started Lot:	2	10	2	
Combined Completed Lots:	2	10	2	
Failures:	0	0	0	
Device on test:	134	543	100	
Mean Test Hour s/Device:	1,070	958	1,128	
Total Device Hours:	143,402	519,986	112,844	

	5			
	Technology:Si Gate CMOSDevice Type:XC17XX/L Microcircuit GroupPackage Type:SOIC-20, VQFP-44Test Condition:T = 85C, R.H. = 85%Bias Voltages:5.0V +/25V			
	XC1701L	XC1702L	XC17XX/L	
Period:	Oct. 1, 1998 to Oct. 1, 2000			
Combined Started Lot:	1	1	2	
Combined Completed Lots:	1	1	2	
Failures:	0	0	0	
Device on test:	45	76	121	
Mean Test Hour s/Device:	1,117	1,048	1,074	
Total Device Hours:	50,265	79,648	129,913	
			<u> </u>	

Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XC17XXXE Microcircuit Group
Package Type:	VOIC-8
Test Condition:	T = 85C, R.H. = 85%
Bias Voltages:	5.0V +/25V

XC17256E

XC17XXXE

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Period:		Oct. 1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	1	
Combined Completed Lots:	1	1	
Failures:	0	0	
Device on test:	45	45	
Mean Test Hour s/Device:	1,024	1,024	
Total Device Hours:	46,080	46,080	

Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined Technology: Si Gate CMOS Device Type: XC17SXX Microcircuit Group Package Type: VOIC-8, PD-8 Test Condition: T = 85C, R.H. = 85% Bias Voltages: 5.0V +/25V					
	XC17S20	XC17S30	XC17S40	XC17SXX	
Period:	: Oct. 1, 1998 to Oct. 1, 2000				
Combined Started Lot:	1	1	1	3	
Combined Completed Lots:	1	1	1	3	
Failures:	0	0	0	0	
Device on test:	45	45	45	135	
Mean Test Hour s/Device:	1,004 1,024 1,117 1,048				
Total Device Hours:	45,180	46,080	50,265	141,525	

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Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined Technology: Si Gate CMOS Device Type: XC18VXX Microcircuit Group Package Type: VQFP-44, SO-20 Test Condition: T = 85C, R.H. = 85% Bias Voltages: 3.3V +/3V				
	XC18V01	XC18V04	XC18VXX	
Period:	Period: Oct. 1, 1998 to Oct. 1, 2000			
Combined Started Lot:	1	1	2	
Combined Completed Lots:	1	1	2	
Failures:	0	0	0	
Device on test:	74	60	134	
Mean Test Hour s/Device:	1,123	1,005	1,070	
Total Device Hours:	83,102	60,300	143,402	

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Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XC95XXX Microcircuit Group
Package Type:	PQFP-160, VQFP-44, CS-48, 144
Test Condition:	T = 85C, R.H. = 85%
Bias Voltages:	5.0V +/25V

XC95108 XC95144 XC9536 XC95216 XC95XXX

Period:		Oct. 1, 1998 to	Oct. 1, 2000			
Combined Started Lot:	1	1	7	1	10	
Combined Completed Lots:	1	1	7	1	10	
Failures:	0	0	0	0	0	
Device on test:	76	76	346	45	543	
Mean Test Hour s/Device:	1,071	1,000	897	1,163	958	
Total Device Hours:	81,396	76,000	310,255	52,335	519,986	
Failure Analysis Number:						
					EXILINX	®

Reliability Testing Summary-Packages Bias Moisture Life Qualification & Monitor Combined

Technology: Si Gate CMOS Device Type: XC95XXXL Microcircuit Group Package Type: PQFP-160 Test Condition: T = 85C, R.H. = 85% Bias Voltages: 3.3V +/- .3V

XC95144XL

XC95XXXXL

Period:	Oct. 1, 1998 to Oct. 1, 2	000
Combined Started Lot:	2	2
Combined Completed Lots:	2	2
Failures:	0	0
Device on test:	100	100
Mean Test Hour s/Device:	1,128	1,128
Total Device Hours:	112,844	112,844
Failure Analysis Number:		
		£`XILINX

Reliability Testing Summary-Packages Pressure Pot Qualification & Monitor Combined					
		Technology:Si Gate CMOSDevice Type:XC17XXX, XC17XXE, XC17SXX, XC95XXXPackage Type:VariousTest Condition:T=121C; 2 atm. sat. steam			
	XC17XX	XC17XXL	XC17XXE	XC17SXX	XC95XXX
Period:		Oct. 1 , 2	1998 to Oct. 1, 2000		
Combined Started Lot:	1	1	1	3	32
Combined Completed Lots:	1	1	1	3	32
Failures:	0	0	0	0	0
Device on test:	75	45	44	134	1,948
Mean Test Hour s/Device:	96	96	186	156	135
Total Device Hours:	72 000	1 320	8 184	20 874	262 560

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Technology:	Si Gate CMOS
Device Type:	XC17XX Microcircuit Group
Package Type:	SOIC-20
Test Condition:	T = 121C; 2 atm. sat. steam

XC1701

XC17XX

Period:	Oct. 1, 1998 to Oct. 1, 200)0
Combined Started Lot:	1	1
Combined Completed Lots:	1	1
Failures:	0	0
Device on test:	75	75
Mean Test Hour s/Device:	96	96
Total Device Hours:	7,200	7,200
Failure Analysis Number:		

Technology:	Si Gate CMOS
Device Type:	XC17XXL Microcircuit Group
Package Type:	PD-8
Test Condition:	T = 121C; 2 atm. sat. steam

XC1701L

XC17XXL

Period:	Oct. 1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	1
Combined Completed Lots:	1	1
Failures:	0	0
Device on test:	45	45
Mean Test Hour s/Device:	96	96
Total Device Hours:	4,320	4,320
Failure Analysis Number:		
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Technology:	Si Gate CMOS
Device Type:	XC17XXXE Microcircuit Group
Package Type:	VOIC-8
Test Condition:	T = 121C; 2 atm. sat. steam

XC17256E

XC17XXXE

Period:	Oct. 1, 1998 to Oct. 1, 200	0
Combined Started Lot:	1	1
Combined Completed Lots:	1	1
Failures:	0	0
Device on test:	44	44
Mean Test Hour s/Device:	186	186
Total Device Hours:	8,184	8,184
Failure Analysis Number:		
		{XILINX®

	Reliability Qualifica	Testing Summ Pressure Po ition & Monito	nary-Packages t or Combined	
	T Do Pac Test	Yechnology: Si Gate Cl evice Type: XC17SXX kage Type: PLCC-20, Condition: T = 121C	MOS Microcircuit Group VOIC-8 ; 2 atm. sat. steam	
	XC17S20	XC17S30	XC17S40	XC17SXX
Period:		Oct. 1, 1998 to O	ect. 1, 2000	
Combined Started Lot:	1	1	1	3
Combined Completed Lots:	1	1	1	3
Failures:	0	0	0	0
Device on test:	45	44	45	134
Mean Test Hour s/Device:	186	186	96	156
Total Device Hours:	8,370	8,184	4,320	20,874
Failure Analysis Number:				£TXILINX®

Technology:	Si Gate CMOS
Device Type:	XC95XXX Microcircuit Group
Package Type:	PLCC-44, CS-48, 144, VQFP-44, TQFP-100, PQFP-100,160
Test Condition:	T = 121C; 2 atm. sat. steam

	XC9536	XC9572	XC95144	XC95216	XC95XXX
Period:		Oct. 1, 199	8 to Oct. 1, 2000		
Combined Started Lot:	5	25	1	1	32
Combined Completed Lots:	5	25	1	1	32
Failures:	0	0	0	0	0
Device on test:	177	1,650	76	45	1,948
Mean Test Hour s/Device:	127	135	168	96	135
Total Device Hours:	22,464	223,008	12,768	4,320	262,560
Failure Analysis Number:					
					_ {XILINX [®]

Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined					
	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XC17XX, XC17XXL, XC17XXXE Various T = -65C / +150C (Air to Air) T = -55C / +125C (Air to Air) for BGA			
	XC17XX	XC17XXL	XC17XXXE		
Period:	Oct.	1, 1998 to Oct. 1, 20	00		
Combined Started Lot:	2	2	1		
Combined Completed Lots:	2	2	1		
Failures:	0	0	0		
Device on test:	91	118	45		
Mean Test Cycles/Device:	965	1,042	1,081		
Total Device Cycles:	87,835	122,960	48,645		
Failure Analysis Number:			{	(XILINX [®] ──	

Oct. 1, 2000 P142

Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined					
	Technology: Device Type: Package Type: Test Condition:		Si Gate CM4 XC17SXX, X Various T = -65C / + T = -55C / +	X & XC95XXXXL BGA	
	XC17SXX	XC	18VXX	XC95XXX	XC95XXXL
Period:		Oct.	1, 1998 to Oct	. 1, 2000	
Combined Started Lot:	3		2	32	5
Combined Completed Lots:	3		2	32	5
Failures:	0		0	0	0
Device on test:	135		132	1,728	344
Mean Test Cycles/Device:	1,061		728	958	1,069
Total Device Cycles:	143,280	90	5,144	1,722,490	367,824
Failure Analysis Number:					{XILINX®

Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XC17XX Microcircuit Group
Package Type:	SOIC-20
Test Condition:	T = -65C/+150C (Air to Air)

XC1701

XC17XX

-**{**`XILINX[®]

Period:	Oct. 1, 1998 to Oct.	1, 2000	
Combined Started Lot:	2	2	
Combined Completed Lots:	2	2	
Failures:	0	0	
Device on test:	91	91	
Mean Test Cycles/Device:	965	965	
Total Device Cycles:	87,835	87,835	
Failure Analysis Number:			
R	eliability Testing Temperature Qualification &	g Summary-Package Cycle (Air to Air) Monitor Combined	S
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	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XC17XXL Microcircuit Group PD-8, VQFP-44 T = -65C/+150C (Air to Air)	
	XC1701L	XC1702L	XC17XXL
Period:	Oct.	1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	1	2
Combined Completed Lots:	1	1	2
Failures:	0	0	0
Device on test:	45	73	118
Mean Test Cycles/Device:	1,021	1,055	1,042
Total Device Cycles:	45,945	77,015	122,960
Failure Analysis Number:			
			── { {XILINX [®] ──

Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XC17XXXE Microcircuit Group
Package Type:	VOIC-8
Test Condition:	T = -65C/+150C (Air to Air)

XC17256E

XC17XXXE

R

Period:	Oct. 1, 1998 to Oct. 1, 2	2000
Combined Started Lot:	1	1
Combined Completed Lots:	1	1
Failures:	0	0
Device on test:	45	45
Mean Test Cycles/Device:	1,081	1,081
Total Device Cycles:	48,645	48,645
Failure Analysis Number:		

	Reliability Tes Temperatu Qualification Techno Device T Backage	sting Summary ure Cycle (Air n & Monitor C logy: Si Gate CMOS Type: XC17SXX Micro	v-Packages to Air) ombined	
	Test Cond	ition: $T = -65C/+150C$	(Air to Air)	
	XC17S20	XC17S30	XC17S40	XC17SXX
Period:		Oct. 1, 1998 to Oct. 1, 2	2000	
Combined Started Lot:	1	1	1	3
Combined Completed Lots:	1	1	1	3
Failures:	0	0	0	0
Device on test:	45	45	45	135
Mean Test Cycles/Device:	1,082	1,081	1,021	1,061
Total Device Cycles:	48,690	48,645	45,945	143,280
Failure Analysis Number:				—{`` XILINX®

Oct. 1, 2000 P147

	Temperature Qualification &	Cycle (Air to Air) Monitor Combined	8
	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XC18VXX Microcircuit Group VQFP-44, SOIC-20 T = -65C/+150C (Air to Air)	
	XC18V01	XC18V04	XC18VXX
Period:	Oct.	1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	1	2
Combined Completed Lots:	1	1	2
Failures:	0	0	0
Device on test:	72	60	152
Mean Test Cycles/Device:	502	1,019	728
Total Device Cycles:	36,144	61,140	96,144
Failure Analysis Number:			€_XILINX [®]

Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined

Technology:	Si Gate CMOS		
Device Type:	XC95XXX Microci	rcuit Group	
Package Type:	PQFP-100,160, PL	CC-44, CS-48, 144, VQ	PFP-44
	TQFP-100, BGA-35	52	
Test Condition:	T = -65C/+150C (A	ir to Air)	
	T = -55C / +125C (A)	Air to Air) for CS* & I	BGA*
		NCO FOC	VCOFAL

XC95108

XC9536*

XC9536

XC95216

Period:		Oct. 1, 1998 to Oct. 1	1, 2000		
Combined Started Lot:	4	3	6	1	
Combined Completed Lots:	4	3	6	1	
Failures:	0	0	0	0	
Device on test:	172	58	370	45	
Mean Test Cycles/Device:	971	1,000	1,008	546	
Total Device Cycles:	167,092	58,000	373,102	24,570	
Failure Analysis Number:					
				—{: XILINX <u>®</u>	

	Reliability Testin Temperature Qualification &	ng Summary e Cycle (Air & Monitor C	y-Packages to Air) combined	
	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XC95XXX Microo PQFP-100,160, PL TQFP-100, BGA-3 T = -65C/+150C (T = -55C / +125C (Circuit Group LCC-44, CS-48, 144, V 352 Air to Air) (Air to Air) for CS* &	QFP-44 BGA*
	XC9572	XC95144*	XC95288*	XC95XXX
Period:	Oct.	1, 1998 to Oct. 1, 20	00	
Combined Started Lot:	16	1	1	32
Combined Completed Lots:	16	1	1	32
Failures:	0	0	0	0
Device on test:	1,032	76	45	1,798
Mean Test Cycles/Device:	948	1,011	1,000	958
Total Device Cycles:	977,890	76,836	45,000	1,722,490
Failure Analysis Number:				= {`` XILINX®

Reliability Testing Summary-Packages Temperature Cycle (Air to Air) Qualification & Monitor Combined

Technology:	Si Gate CMOS
Device Type:	XC95XXXL Microcircuit Group
Package Type:	PQFP-160, 208, TQFP144, CS-144-280
Test Condition:	T = -65C/+150C (Air to Air)

XC95144XL XC95144XL* XC95288XL XC95288XL* XC95XXXX	XL
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Period:		Oct. 1, 19	998 to Oct. 1, 2000			
Combined Started Lot:	2	1	1	1	5	
Combined Completed Lots:	2	1	1	1	5	
Failures:	0	0	0	0	0	
Device on test:	151	41	76	76	344	
Mean Test Cycles/Device:	1,145	1,012	1,018	1,000	1,069	
Total Device Cycles:	172,964	41,492	77,368	76,000	367,824	
Failure Analysis Number:						
					={: XILINX	R

Technology:	Si Gate CMOS
Device Type:	XC95XXX Microcircuit Group
Package Type:	Various
Test Condition:	T = 130C, R.H. = 85%
Bias Voltage:	5.0V +/25V

XC95XXX

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Period:	Oct. 1, 1998 to Oct. 1, 2000
Combined Started Lot:	4
Combined Completed Lots:	4
Failures:	0
Device on test:	95
Mean Test Hours/Device:	288
Total Device Hours:	27,400

J	Reliability Testing I Qualification &	g Summary-Pac Hast Monitor Combi	kages ned	
	Technology: Device Type: Package Type: Test Condition: Bias Voltage:	Si Gate CMOS XC95XXX PQFP-160, PLCC-44 T = 130C, R.H. = 85% 5.0V +/25V		
	XC9572	XC95216	XC95XXX	
Period:	Oct.	1, 1998 to Oct. 1, 2000		
Combined Started Lot:	3	1	4	
Combined Completed Lots:	3	1	4	
Failures:	0	0	0	
Device on test:	80	15	95	
Mean Test Hours/Device:	286	300	288	
Total Device Hours:	22,900	4,500	27,400	
			{	

	Reliability Tes Da Qualification	ting Summary ta Retention & Monitor C	-Packages ombined	
	Techno Device Package Test Cond	logy: Si Gate CMOS Type: XC17XXXE, XC Microcircuit Gr Type: Various ition: 150C	C17XXL, XC17SXX, X oup	XC17SXXXL
	XC17XXXE	XC17XXL	XC17SXX	XC17SXXXL
Period:		Oct. 1, 1998 to Oct. 1, 2	2000	
Combined Started Lot:	2	6	3	1
Combined Completed Lots:	2	6	3	1
Failures:	0	0	0	0
Device on test:	285	512	418	138
Mean Test Hours/Device:	1,627	1,622	1,766	2,171
Total Device Hours:	463,712	830,442	738,091	299,598
Failure Analysis Number:				—{XILINX®—

	Reliability Testing Data F Qualification & I	Summary-Package Retention Monitor Combined	es
	Technology: Device Type: Package Type: Test Condition:	Si Gate CMOS XC18VXX, XC95XXX, XC95 Various 150C	XXXXL Microcircuit Group
	XC18VXX	XC95XXX	XC95XXXXL
Period:	Oct. 1	l, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	7	1
Combined Completed Lots:	1	7	1
Failures:	0	0	0
Device on test:	60	589	22
Mean Test Hours/Device:	1,021	2,043	2,130
Total Device Hours:	61,260	1,203,548	46,860
Failure Analysis Number:			
			── { {XILINX [®]

Technology:Si Gate CMOSDevice Type:XC17XXXE Microcircuit GroupPackage Type:PD-8Test Condition:150C

XC17256E

XC17XXXE

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Period:	Oct. 1, 1998 to Oct. 1,	2000
Combined Started Lot:	2	2
Combined Completed Lots:	2	2
Failures:	0	0
Device on test:	285	285
Mean Test Hours/Device:	1,627	1,627
Total Device Hours:	463,712	463,712

	Reliability Tes Da Qualification	ting Summary-Pack ta Retention & Monitor Combin	kages ned
	Techno Device ' Package ' Test Cond	blogy: Si Gate CMOS Type: XC17XXL Microcircuit (Type: PD-8, VQFP-44 lition: 150C	Group
	XC1701L	XC1704L	XC17XXL
Period:		Oct. 1, 1998 to Oct. 1, 2000	
Combined Started Lot:	4	2	6
Combined Completed Lots:	4	2	6
Failures:	0	0	0
Device on test:	296	216	512
Mean Test Hours/Device:	1,793	1,388	1,622
Total Device Hours:	530,730	299,712	830,442
			{XILINX®

	Reliability Testir Data Qualification &	ng Summary-Pa Retention Monitor Com	ckages oined	
	Technolog Device Typ Package Typ Test Condition	y: Si Gate CMOS e: XC17SXX Microcircu e: PD-8 n: 150C	it Group	
	XC17S30	XC17S40	XC17SXX	
Period:	Oc	t. 1, 1998 to Oct. 1, 2000		
Combined Started Lot:	2	1	3	
Combined Completed Lots:	2	1	3	
Failures:	0	0	0	
Device on test:	285	133	418	
Mean Test Hours/Device:	1,627	2,063	1,766	
Total Device Hours:	463,712	274,379	738,091	
			{XILINX®	

Technology:Si Gate CMOSDevice Type:XC17SXXXL Microcircuit GroupPackage Type:PD-8Test Condition:150C

XC17S10XL

XC17SXXXL

€XILINX[®]

Period:	1998 to Oct. 1, 2000	
Combined Started Lot:	1	1
Combined Completed Lots:	1	1
Failures:	0	0
Device on test:	138	138
Mean Test Hours/Device:	2,171	2,171
Total Device Hours:	299,598	299,598

Technology:Si Gate CMOSDevice Type:XC18VXX Microcircuit GroupPackage Type:VQFP-44Test Condition:150C

XC18V04

XC18VXX

€XILINX[®]

Period:	Oc	Oct. 1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	1	
Combined Completed Lots:	1	1	
Failures:	0	0	
Device on test:	60	60	
Mean Test Hours/Device:	1,021	1,021	
Total Device Hours:	61,260	61,260	

	Reliability Qualific	y Testing Su Data Rete ation & Mo Technology: Si G Device Type: XC9 ackage Type: PLC est Condition: 1500	ention ention nitor Combi ate CMOS 5XXX Microcircuit CC- 44, 84, PQFP-166	kages ned Group 0, HQFP-208	
	XC95108	XC9572	XC95216	XC9536	XC95XXX
Period:		Oct. 1, 199	8 to Oct. 1, 2000		
Combined Started Lot:	3	1	1	2	7
Combined Completed Lots:	3	1	1	2	7
Failures:	0	0	0	0	0
Device on test:	196	107	105	181	589
Mean Test Hours/Device:	2,516	1,213	2,057	2,014	2,043
Total Device Hours:	493,071	129,791	215,985	364,701	1,203,548
Failure Analysis Number:					-\$ *XILINX®

Technology:Si Gate CMOSDevice Type:XC95XXXXL Microcircuit GroupPackage Type:PQFP-160Test Condition:150C

XC95144XL

XC95XXXXL

Period:	Oct. 1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	1
Combined Completed Lots:	1	1
Failures:	0	0
Device on test:	22	22
Mean Test Hours/Device:	2,130	2,130
Total Device Hours:	46,860	46,860
Failure Analysis Number:		
		€`XILINX®

]	Reliability Testing Erase Qualification &	s Summary-Pac Cycling Monitor Combi	kages ined
	Technology: Device Type: Package Type: Test Condition: Voltage:	Si Gate CMOS XC18VXX Microcircuit PLCC- 44 85C Vcc=3.0V, Vpp=9.0-9.5V	Group
	XC18V04	XC18VX	X
Period:	Oct. 1, 1998 to Oct. 1, 2000		
Combined Started Lot:	1	1	
Combined Completed Lots:	1	1	
Failures:	0	0	
Device on test:	30	30	
	16.000	16,000	
Mean Test Cycles/Device:	10,000		

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	Reliability Testing Summary-Packages Erase Cycling Qualification & Monitor Combined						
	Technology Device Type Package Type Test Condition Voltage	 Si Gate CMOS XC95XXX Microcircuit Group PLCC- 84 55C Vcc=5.0V, Vpp=12.0-12.5V 					
	XC9536	XC95108	XC95XXX				
Period:	Oct	. 1, 1998 to Oct. 1, 2000					
Combined Started Lot:	1	1	2				
Combined Completed Lots:	1	1	2				
Failures:	0	0	0				
Device on test:	29	80	109				
Mean Test Cycles/Device:	10,000	10,939	10,689				
Total Device Cycles:	290,000	875,120	1,165,120				
			&XILINX®				

	Reliability Testing Erase Qualification &	g Summary-Package e Cycling Monitor Combined	S
	Technology: Device Type: Package Type: Test Condition: Voltage:	Si Gate CMOS XC95XXX Microcircuit Group PLCC- 84, PC44 85C Vcc=5.0V, Vpp=12.0-12.5V	
	XC9536	XC9572	XC95XXX
Period:	Oct.	1, 1998 to Oct. 1, 2000	
Combined Started Lot:	1	1	3
Combined Completed Lots:	1	1	3
Failures:	0	0	0
Device on test:	16	28	44
Mean Test Cycles/Device:	30,000	10,000	17,273
Total Device Cycles:	480,000	280,000	760,000
			€_XILINX®

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Reliability Testing Summary-Packages Erase Cycling Qualification & Monitor Combined

Technology: Si Gate CMOS Device Type: XC95XXXL Microcircuit Group Package Type: PQFP-160 Test Condition: -40C Voltage: Vcc=3.3V, Vpp=9.0-9.5V

XC95144XL

XC95XXXXL

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Period:	Oct. 1, 1998 to Oct. 1	, 2000
Combined Started Lot:	1	1
Combined Completed Lots:	1	1
Failures:	0	0
Device on test:	22	22
Mean Test Cycles/Device:	19,546	19,546
Total Device Cycles:	430,000	430,000

Package Qualification & Monitor Program

EXILINX:

Device Package Attach Mat ing Comp bined Lots	Type: XC1 Type: PD8 iterial: Silve oound: Sum Failures	1701L, XC17256 8 er Epoxy nitomo 6300H & Device On Test	6E & Shenitsu KMC Mean Test Hrs/Cycles	C-1805 Total Device Hrs
bined Lots	Failures 0	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs
	0	15		
1		43	1,021	45,945
1	0	45	96	4,320
1	0	45	1,000	50,265
2	0	6		
2	0	6		
2	0	6		
•	0	10		
	2 2 2	2 0 2 0 2 0	2 0 6 2 0 6 2 0 10	2 0 6 2 0 6 2 0 10

Reliability Testing Summary Package Qualification / Monitor SOIC Device Type: XC1701, XC18V01, XCR22V10 Package Type: SOIC-20, 24 Die Attach Material: Silver Epoxy Molding Compound: EME6300H, MP8000-CH4						
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs	
T/C	3	0	163	761	123,979	
Pressure Pot	2	0	148	132	19,464	
85/85	1	0	74	1,123	83,102	
Solderability	1	0	3			
Lead Fatigue	2	0	8			
Physical Dimension	2	0	10			
Resistance to Solvents	1	0	3			
Bond Pull	3	0	15			
Period:	Oct 1st, 1998 to Oct. 1st	. , 2000			_ \$^ XII INX <u>®</u>	

Reliability Testing Summary Package Qualification / Monitor TSOP Device Type: XC17S20, 17256E, XCR22V10 Package Type: VO8, VO24 Die Attach Material: Silver Epoxy Molding Compound: KMC 184-3, MP8000-CH4						
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs	
T/C	2	0	90	1,082	97,335	
Pressure Pot	2	0	89	186	16,554	
85/85	2	0	90	1,014	91,260	
Solderability	3	0	9			
Physical Dimension	5	0	25			
Resistance to Solvents	3	0	9			
Lead Fatigue	3	0	10			
Bond Pull	2	0	10			
Period: (Oct.1st, 1998 to Oct. 1st	, 2000			_ \$ [™] XII IN X ®	

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	Reliability Package Qu	y Testing Jalificatio PLCC-44	Summary on / Monit 4	or	
	Device Type Package Type Die Attach Materia Molding Compound	e: XC3030/A XC1704L e: PLCC- 44 l: Silver Epo l: Sumitomo	A, XC9536, X 4 oxy o 6300H, MP8	C9572, 000	
Reliability Test	Combined No. Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs
T/C	14	0	826	926	765,098
Pressure Pot	19	0	1,134	124	140,448
Hast	3	0	80	286	22,900
Solderability	2	0	6		
Resistance to Solvents	3	0	9		
Lead Fatigue	2	0	6		
Physical Dimension	2	0	10		
Bond Pull	3	0	13		
Die Shear	2	0	8		
Period	: Oct. 1st, 1998 to Oct. 1st, 20	000			∑XII INX <u>®</u>

	Reliabili Package Q I	ty Testing Qualification PLCC-68,	Summary on / Monit 84	y or	
	Device Typ Package Tyj Die Attach Materi Molding Compour	pe: XC3030/A pe: PLCC- 68 al: Silver Epo ad: Sumitomo	A, XC4005E, 2 3, 84 DXY D 6300H, MP8	XC4006E, XC40 000	10/XL
Reliability Test	Combined No. Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs
T/C	2	0	152	1,019	154,888
Pressure Pot	4	0	186	88	16,296
Hast	1	0	36	300	10,800
85/85	2	0	66	1,004	66,270
Solderability	3	0	9		
Resistance to Solvents	3	0	9		
Lead Fatigue	3	0	10		
Physical Dimension	3	0	15		
Bond Pull	2	0	10		
Adhesion to lead finish	1	0	4		
Period	: Oct. 1st, 1998 to Oct. 1st, 2	2000			

	Reliabili Package Q	ty Testing Jualificati PQFP-1	g Summai ion / Moni 00	ry tor		
Device Type: XC3042/A, XC9572 Package Type: PQFP- 100 Die Attach Material: Silver Epoxy Molding Compound: Sumitomo 6300H, EME-7304LC, E7N36 &						
Reliability Test	Combined No. Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs	
T/C	4	0	304	1,014	308,332	
Pressure Pot	4	0	302	150	45,264	
85/85	1	0	45	1,117	50,265	
Bond Pull	1	0	5			
Physical Dimension	1	0	5			
Period:	Oct. 1st, 1998 to Oct. 1st,	2000			_ {` XILINX®	

	Reliabilit Package Q	y Testing ualificati PQFP-10	g Summai ion / Moni 60	ry itor		
Device Type: XC95216, XC95144/XL, XC5206, XC4013E, XC4006 Package Type: PQFP- 160 Die Attach Material: Silver Epoxy Molding Compound: Sumitomo 6300H, EME-7304LC, E7N36 & 1						
Reliability Test	Combined No. Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs	
T/C	7	0	338	991	334,806	
Pressure Pot	2	0	89	96	8,544	
Hast	1	0	15	300	4,500	
85/85	3	0	197	1,118	220,295	
Die Shear	1	0	5			
Resistance to Solvents	1	0	3			
Bond Pull	1	0	5			
Period: (Oct. 1st, 1998 to Oct. 1st, 2	000				

	Reliabili Package Q	ty Testing Qualificati PQFP-20	g Summa ion / Moni 08	ry itor	
	Device Ty Package Ty Die Attach Mater Molding Compou	pe: XC4010E XC952882 pe: PQFP- 2 ial: Silver E nd: Sumiton	, XC4020XL, X0 XL, 208 poxy no 6300H, EN	CS30XL,XCS40XL, 1E-7304LC, E7N	XC2S150 736 & MP8000
Reliability Test	Combined No. Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs
T/C	18	0	849	975	828,033
Pressure Pot	2	0	80	137	10,920
Hast	1	0	12	300	3,600
85/85	1	0	45	1,148	51,660
Solderability	2	0	6		
Resistance to Solvents	2	0	6		
Lead Fatigue	2	0	6		
Physical Dimension	2	0	10		
Salt Atmosphere	2	0	30		
Bond Pull	1	0	5		
Period	: Oct. 1st, 1998 to Oct. 1st,	2000			

	Reliabili Package (ty Testing Jualificati PQFP-24	g Summai ion / Moni 40	ry tor		
Device Type: XC4013/E, XC4013XL, XC4025E, XC4010E XCS30/XL, XCV100, XCV300, XCV300EXC2S150 Package Type: PQFP- 240 Die Attach Material: Silver Epoxy Molding Compound: Sumitomo 6300H, EME-7304LC, E7N36 & MP800						
Reliability Test	Combined No. Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs	
T/C	13	0	618	1,012	625,526	
Pressure Pot	9	0	399	105	42,024	
Hast	6	0	170	135	23,000	
85/85	6	0	268	1,003	268,832	
Solderability	3	0	9			
Bond Pull	1	0	5			
Lead Fatigue	3	0	9			
Salt Atmosphere	2	0	30			
Mark Permaanency	5	0	15			
Period	: Oct. 1st, 1998 to Oct. 1st,	2000				

Reliability Testing Summary Package Qualification / Monitor TQFP Device Type: XC3190/A, XC4010XL, XC9572, XC95144XL XCS30XL, XCR3256XL, XCV100 Package Type: TQFP- 100, 144 & 176 Die Attach Material: Silver Epoxy Molding Compound: EME-7320, E7N32 Reliability Combined Device Mean Test Total					
Test	No. Lots	Failures	On Test	Hrs/Cycles	Device Hrs
T/C	8	0	558	1,029	574,025
Pressure Pot	7	0	420	157	65,736
85/85	2	0	71	1,054	74,869
Solderability	3	0	9		
Resistance to Solvents	4	0	12		
Lead Fatigue	3	0	10		
Physical Dimension	3	0	15		
Bond Pull	1	0	5		
Period: C)ct. 1st, 1998 to Oct. 1st, 1	2000			

Reliability Testing Summary Package Qualification / Monitor VQFP						
Reliability Test	Device Typ Package Typ Die Attach Materia Molding Compoun Combined No.Lots	e: XC303 XC953 e: VQFP- d: Silver I d: EME-7 Failures	: XC3030/A/L, XC4003E, XCS30XL, XC9536, XC1702L, XC5202, XC1804 : VQFP- 44, 64, 100 : Silver Epoxy : EME-7320 Device Mean Test Total Sailures On Test Hrs/Cycles Device Hit			
T/C	5	0	315	1,027	323,563	
Pressure Pot	5	0	286	158	45,216	
85/85	8	0	382	900	343,919	
Resistance to Solvents	4	0	12			
Bond pull	1	0	5			
Lead Fatigue	4	0	12			
Physical Dimension	4	0	20			
Solderability	4	0	12			
Adhesion to lead finish	1	0	3			
Period: O	ct. 1st, 1998 to Oct. April 20	00				

Reliability Testing Summary Package Qualification / Monitor HQFPDevice Type:XC4020E, XC4013E, XC4028EX, XC4036XLA, XC4062XLA,XC4044XLA, XC4052XLA,XC4085XLA XC40150XV, XCV300, XCV800,XCV1000/EPackage Type:HQFP- 240 & 304Die Attach Material:84-1LMSR4Molding Compound:Sumitomo 7304L						
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs	
T/C	14	1 **	910	1,009	918,122	
Pressure Pot	6	0	237	116	27,576	
Hast	8	0	146	179	26,200	
85/85	2	0	89	1,007	89,629	
Resistance to Solvents	3	0	9			
Lead Fatigue	3	0	9	**F/A-99036(1)-CRCP@1005cy.		
Physical Dimension	4	0	20			
Solderability	3	0	9			
Salt Atmosphere	2	0	30			
Bond Pull	2	0	10			
Period: O	ct. 1st, 1998 to Oct. 1st, 20	00		;	\$ ************************************	

Reliability Testing Summary Package Qualification / Monitor PPGA Device Type: XC3190/A Package Type: PPGA-132, 175 Die Attach Material: Silver Epoxy Sealant Material: R4785								
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs			
T/C	1	0	45	1,060	47,700			
Pressure Pot	2	0	90	96	8,640			
85/85	2	0	89	1,005	89,441			
Solderability	2	0	6					
Lead Fatigue	2	0	6					
Physical Dimension	2	0	10					
Bond Strength	1	0	5					
Die shear	1	0	5					
Period: Ja	an. 1st, 1997 to Oct. 1st, 2	2000			_ \$* XII INX®			
Reliability Testing Summary Package Qualification / Monitor HTFP								
--	---	--	--	----------------	-------------------	--	--	--
	Device T Package T Die Attach Mate Molding Compo	Ype:XC30Ype:HT-14Prial:Silverund:73200	90A, XC4010 44, 176, 208 Epoxy CR	, XC4020XL, XC	C3090/A			
Reliability	Combined		Device	Mean Test	Total			
Test	No.Lots	Failures	On Test	Hrs/Cycles	Device Hrs			
T/C	4	0	242	655	158,592			
Pressure Pot	3	0	137	96	13,152			
85/85	3	0	166	1,022	169,662			
Resistance to Solvents	1	0	3					
Physical Dimension	1	0	5					
Lead Integrity	1	0	3					
Solderability	1	0	3					
Adhesion to lead finish	1	0	3					
Period: Jan	n. 1st, 1996 to Oct. 1st, 2	000						

Reliability Testing Summary Package Qualification / Monitor BGA-225, 256 Device Type: XC4013/XL/XLA, XC4020XL/XLA Package Type: BGA-225, 256, Die Attach Material: Silver Epoxy Test Condition: -55C/+125C for T/C								
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs			
T/C	5	0	187	1,020	190,764			
Pressure Pot	2	0	197	124	24,384			
85/85	1	0	74	1,010	74,756			
Ball Shear	1	0	5					
Salt Atmosphere	1	0	15					
Period	: Oct. 1st, 1998 to Oct. 1st, 2	2000			€`XILINX <u>®</u>			

	Reliabilit Package Q	ty Testing ualificati BGA-35	g Summar on / Moni [*] 2	y tor	
	Device T Package T Die Attach Mate Test Condi	Cype:XC40Cype:BGA-erial:Silverition:-55C/-	36XL,XC4028 432 Epoxy +125C for T/C	3XL,XCV300, X(C	C 95288
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs
T/C	6	0	162	1,004	162,638
Pressure Pot	3	0	32	96	3,072
Salt Atmosphere	1	0	15		
Period:	Oct. 1st, 1998 to Oct. 1st, 2	2000			

	Reliabilit Package Q	ty Testing Jualificati BGA-43	g Summar on / Moni 2	y tor	
	Device 7 Package 7 Die Attach Mat Test Cond	Гуре: XC40 Гуре: BGA- erial: Silver ition: -55C/	952XL, XC406 - 432 : Epoxy +125C for T/C	2XL, XCV800, X C	CV600
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs
T/C	4	0	110	1,007	110,792
T/C Pressure Pot	4 2	0 0	110 72	1,007 96	110,792 6,912
T/C Pressure Pot 85/85	4 2 1	0 0 0	110 72 16	1,007 96 1,166	110,792 6,912 18,656
T/C Pressure Pot 85/85 Physical Dimension	4 2 1 1	0 0 0 0	110 72 16 5	1,007 96 1,166	110,792 6,912 18,656
T/C Pressure Pot 85/85 Physical Dimension Ball Shear	4 2 1 1 1	0 0 0 0 0	110 72 16 5 5	1,007 96 1,166	110,792 6,912 18,656

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Period: Oct. 1st, 1998 to Oct. 1st, 2000

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	Reliabilit Package Q	y Testing ualificati BGA-56	g Summar on / Moni ⁻ 0	y tor		
Device Type: XC4062XL/XLA, XC4085XL/XLA, XC40125XV, XC40150 XCV800, XCV1000, XCV1000E, XCV2000E Package Type: BGA-560 Die Attach Material: Silver Epoxy Test Condition: -55C/+125C for T/C						
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs	
T/C	14	0	387	932	360,529	
Pressure Pot	8	0	194	104	20,208	
85/85	3	0	50	1,136	56,796	
Hast	3	0	45	100	4,500	
Resistance to Solvents	2	0	6			
Bond Pull	3	0	15			
Ball Shear	3	0	15			
Physical Dimension	1	0	5			
Salt Atmophere	2	0	18			
Period: O	ct. 1st, 1998 to Oct. 1st, 2	2000				

	Reliabili Package Q	ty Testing ualificati BGA-72	g Summar on / Monit 8	y tor					
Device Type: XCV1000E Package Type: BGA-728 Die Attach Material: 8510AA Test Condition: -55C/+125C for T/C									
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs				
T/C	1	0	26	1,148	29,847				
Pressure Pot	1	0	29	168	4,872				
Hast	1	0	21	102	2,142				
Bond Pull	1	0	5						
Ball Shear	1	0	5						
Peri	od: Oct. 1st, 1998 to Oct. 1st,	2000							

Reliability Testing Summary Package Qualification / Monitor CS-48								
Device Type: XC9536 Package Type: CS-48, Die Attach Material: Silver Epoxy Test Condition: -55C/+125C for T/C								
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs			
T/C	3	0	58	1,000	58,000			
Pressure Pot	4	0	132	132	18,144			
85/85	3	0	195	1,054	205,549			
Resistance to Solvents	1	0	3					
Physical Dimension	1	0	5					
Ball Shear	1	0	5					
Bond Pull	1	0	5					
Period: Jul	ly 1st, 1998 to Oct. 1st, 2	2000			S XILINX <u></u>			

Reliability Testing Summary Package Qualification / Monitor CS-144, 280							
Device Type: XC95144, XC95288XL, XCV100,XCV200E, XC8 XCR3128XL, Package Type: CS -144, -280 Die Attach Material: Silver Epoxy Test Condition: -55C/+125C for T/C							
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs		
T/C	3	0	179	1,034	185,106		
Pressure Pot	3	0	179	152	27,120		
Hast	1	0	27	148	4,000		
85/85	2	0	119	1,044	124,375		
Resistance to Solvents	3	0	11				
Physical Dimension	3	0	15				
Ball Shear	5	0	25				
Bond Pull	5	0	25				
Die Shear	1	0	4				
Period: (Oct. 1st, 1998 to Oct. 1st, 2	.000			E XILINX <u>®</u>		

Reliability Testing Summary Package Qualification / Monitor FG-256 Device Type: XCV200, XCV50 Package Type: FG-256 Die Attach Material: Silver Epoxy Test Condition: -55C/+125C for T/C							
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs		
T/C	5	0	165	1,031	170,062		
Pressure Pot	3	0	148	133	19,680		
Hast	2	0	42	150	6,300		
Resistance to Solvents	1	0	3				
Physical Dimension	1	0	5				
Poriod: Oc	t 1st 1998 to Oct 1st 3	2000			A		

	Reliability Testing Summary Package Qualification / Monitor FG-456, 556							
Device Type: XCV1000, XCV300E, XCV300 Package Type: FG-456, 556 Die Attach Material: Silver Epoxy Test Condition: -55C/+125C for T/C								
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs			
T/C	6	0	108	1,032	111,478			
Pressure Pot	1	0	22	168	3,696			
Hast	1	0	8	300	2,400			
Resistance to Solvents	1	0	3					
Physical Dimension	1	0	5					
Ball Shear	1	0	5					
Bond Pull	2	0	7					
Period: Oct	t. 1st, 1998 to Oct. 1st, 2	.000			≶ TXILINX [®]			

Reliability Testing Summary Package Qualification / Monitor FG-676								
	Device T Package T Die Attach Mate Test Condi	Device Type: XCV800 Package Type: FG-676 tach Material: Silver Epoxy Yest Condition: -55C/+125C for T/C						
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs			
T/C	1	0	22	1,000	22,000			
Pressure Pot	1	0	22	96	2,112			
Resistance to Solvents	1	0	3					
Ball Shear	1	0	5					
Bond Pull	1	0	5					
Period: Oc	t. 1st, 1998 to Oct. 1st, 2	000			\$ *XII INX_®			

	Reliabili Package Q	ty Testing Jualificati FG-680	g Summar on / Monit	y tor	
	Device 7 Package 7 Die Attach Mate Test Cond	Type:XCV1Type:FG-68erial:Silverition:-55C/-	.000 80 Epoxy +125C for T/C		
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs
T/C	1	0	34	1,000	34,000
Pressure Pot	1	0	31	96	2,976
Ball Shear	1	0	5		
Bond Pull	1	0	5		
		2000			
Perio	d: Oct. 1st, 1998 to Oct. 1st, 2	2000			. 🗶 XILINX 👛

	Reliabilit Package Q	y Testing ualificati FG-900	g Summar ion / Moni ⁻)	y tor	
	Device T Package T Die Attach Mate Test Condi	Sype:XCVSype:FG-9erial:Silvertion:-55C/	1000E, XCV16 00 r Epoxy ′+125C for T/C	000E, XCV812E	
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs
T/C	3	0	74	1,070	79,190
Hast	3	0	66	100	6,600
Pressure Pot	2	0	54	168	9,072
Resistance to Solvents	1	0	3		
Ball Shear	1	0	5		
Bond Pull	1	0	5		
Physical Dimension	1	0	5		
Period: Oc	t. 1st, 1998 to Oct. 1st, 2	2000			

	Reliabilit Package Q	ty Testing ualificati FG-115	g Summar on / Moni 6	y tor	
	Device T Package T Die Attach Mate Test Condi	Cype:XCV1Cype:FG-11crial:Silvertion:-55C/-	1000E 156 • Epoxy +125C for T/C		
Reliability Test	Combined No.Lots	Failures	Device On Test	Mean Test Hrs/Cycles	Total Device Hrs
T/C	3	0	38	821	31,188
Hast	1	0	22	100	2,200
Pressure Pot	1	0	22	168	3,696
Resistance to Solvents	1	0	3		
Ball Shear	1	0	5		
Bond Pull	1	0	5		
Physical Dimension	1	0	5		
Period: Oc	t. 1st, 1998 to Oct. 1st, 2	2000			

Reliability Testing Summary PGA Package Qualification / Monitor PGA-84, -120, -132, -156, -175, -191, -223, -299

	Co	ombined		Mean Hrs/Cycles	Total
Code	Test	Sample	Failures	Per Device	Device Hours
B2	Resistance to Solvents	102	0		
B3	Solderability	105	0		
B5	Bond Strength	102	0		
D1	Physical Dimension	75	0		
D2	Lead Integrity	21	0		
	Seal				
D3	Thermal Shock	105	0	15	1,575
	Temperature Cycle			100	10,500
	Seal				,
	Visual Examination				
	End-Point Elect.				
	Parametrics				
D4	Mechanical Shock	105	0		
	Vibration, Var. Freq.				
	Constant Accel.				
	Seal				
	Visual Examination				
	End-Point Elec. Para	•			
D5	Salt Atmosphere	105	0		
	Seal				
	Visual Examination	• 1	0		
D6	Internal Water-Vapor Conte	ent 21	0		
D7	Adhesion of lead finish	21	0		
	Period: Oct. 1st, 1998	to Oct. 1st, 2000)		

Code B2 R B3 So B5 B6 D1 P1 D2 L0 D3 T1	Contract Test Resistance to Solvents olderability Sond Strength Physical Dimension Lead Integrity Seal	ombined Sample 124 129 95 135 27	Failures 0 0 0 0	Mean Hrs/Cycles Per Device	Total Device Houi
B2 R B3 So B5 Bo D1 Pl D2 Lo D3 Tl	Resistance to Solvents olderability Bond Strength Physical Dimension Lead Integrity Seal	124 129 95 135 27	0 0 0 0		
B3 So B5 Bo D1 Pl D2 Lo D3 Tl	olderability Sond Strength Physical Dimension Lead Integrity Seal	124 129 95 135 27	0 0 0 0		
B5 B/ D1 Pl D2 L/ D3 Tl	Sond Strength Physical Dimension Lead Integrity Seal	95 135 27			
D1 Pl D2 La D3 Tl	Physical Dimension Lead Integrity Seal	135 27	0		
D2 La D3 T	ead Integrity Seal Charmal Shooly	27	0		
D3 T	Seal Thermal Shack				
D3 T	harmal Chaol		U		
	Temperature Cycle	147	0	15 100	2,20 14,70
D4 M	Seal Visual Examination End-Point Elect. Parametrics Aechanical Shock Vibration, Var. Freq. Constant Accel. Seal Visual Examination End-Point Elec. Para.	135	0		
D5 Sa	alt Atmosphere Seal Visual Examination	150	0		
D6 In	nternal Water-Vapor Content	t 27	0		
D7 A	dhesion of lead finish	27	Ň		

] DD8	Reliability Package (Testing Sur Qualification	mmary n / Monitor	
Code	C Test	Combined Sample	Failures	Mean Hrs/Cycles Per Device	Total Device Hours
B2	Resistance to Solvents	18	0		
B3	Solderability	21	Õ		
B5	Bond Strength	$\overline{31}$	Õ		
D1	Physical Dimension	60	Ō		
D2	Lead Integrity	30	0		
D3	Thermal Shock Temperature Cycle Seal Visual Examination End-Point Elect. Parametrics	105	0	15 100	1,575 10,500
D4	Mechanical Shock Vibration, Var. Freq. Constant Accel. Seal Visual Examination End-Point Elec. Para.	105	0		
D5	Salt Atmosphere Seal Visual Examination	105	0		
D6	V ISUAI EXAMINIATION Internal Water-Vanor Conte	nt 15	0		
D7	Adhesion of lead finish	15	0		
D8	Lead Torque	20	0		
	Period: Oct. 1st, 199	8 to Oct. 1st, 200	0		

	C	combined		Mean Hrs/Cycles	Total
Code	Test	Sample	Failures	Per Device	Device Hours
B2	Resistance to Solvents	18	0		
B3	Solderability	3	0		
B5	Bond Strength	4	0		
D1	Physical Dimension	15	0		
D2	Lead Integrity Seal	3	0		
D3	Thermal Shock	15	0	15	225
	Temperature Cycle Seal Visual Examination End-Point Elect.			100	1,500
D4	Parametrics Mechanical Shock Vibration, Var. Freq. Constant Accel. Seal	15	0		
D5	Visual Examination End-Point Elec. Para. Salt Atmosphere Seal	15	0		
D6	visual Examination Internal Water-Vanar Contor	at 3	0		
D7	Adhesion of lead finish	3	Ō		
D9	Lead Torque	5	Ō		

Reliability Testing Summary-Packages EIAJ Temperature Soldering Heat Test

	To De Pacl Pre-conditionning Test Test Solder Ho Test	echnology: Si- vice Type: XC kage Type: PD Assembly: AA Condition: T = Duration: 240 eat Temp.: 350 Duration: 3 +	Gate CMOS C17XXX Microcircuit 8, SO20, VO8, VQ44 .PI = 85C, R.H. = 85%) hours) +/- 10 degrees C 0.5/-0 seconds	Group	
	XC17S20	XC17S40	XC17128E	XC1702L	XC17XXX
Period	:	Oct. 1, 19	97 to Oct. 1, 2000		
Combined Started Lot	: 1	1	1	1	4
Combined Completed Lots	: 1	1	1	1	4
Failures	: 0	0	0	0	0
Device on test	: 3	3	3	3	12
Failure Analysis	:				
Note : Solder	ability test applied to all	leads			

• **{ `** XILINX ®

	Reliability Testing EIAJ Temperatur	g Summary-Packages e Soldering Heat Test	
	Technology: Device Type: Package Type: Assembly: Pre-conditionning Test Condition: Test Duration: Solder Heat Temp.: Test Duration:	Si-Gate CMOS XC3XXX/A Microcircuit Group PLCC-44, VQFP-100 Anam T = 85C, R.H. = 85% 240 hours 350 +/- 10 degrees C 3 + 0.5/-0 seconds	
	XC3030/A	XC3042/A	XC3XXX/A
Period	l: Oct.	1, 1997 to Oct. 1, 2000	
Combined Started Lot	: 1	1	2
Combined Completed Lots	: 1	1	2
Failures	• 0	0	0
Device on test:	3	3	6
Failure Analysis	:		
Note : Solde	rability test applied to all leads		« • • • • • • • • • • • • • • • • • • •
			──Z. XILINX——

Ρ	Reliabi EIAJ T Pre-conditionning Sole	ility Testin emperatu Technology: Device Type: Package Type: Assembly: Test Condition: Test Duration: der Heat Temp.: Test Duration:	ng Summa Si-Gate CMC XC4XXXE, X PLCC- 84, PC Anam T = 85C, R.H 240 hours 350 +/- 10 deg 3 + 0.5/-0 seco	ry-Packag ng Heat To os xC4xxxxL, XC4 QFP-240, HQFP1 5. = 85% grees C onds	es est ⁴ XXXXLA Mici 60, 304, HT-144	ocircuit Group
	XC4003E	XC4013E	XC4085XLA	XC4013XL	XC4044XL	XC4XXX
Period:		0	ct. 1, 1997 to Oct.	1, 2000		
Combined Started Lot:	1	1	1	1	1	5
Combined Completed Lots:	1	1	1	1	1	5
Failures:	0	0	0	0	0	0
Device on test:	3	3	3	3	3	15
Failure Analysis:						
Note : Soldera	bility test applied	to all leads			<u> </u>	XILINX®

	Reliability Testing EIAJ Temperatur	g Summary-Packages e Soldering Heat Test	
	Technology: Device Type: Package Type: Assembly: Pre-conditionning Test Condition: Test Duration: Solder Heat Temp.: Test Duration:	Si-Gate CMOS XC5XXX Microcircuit Group TQFP-176 Anam T = 85C, R.H. = 85% 240 hours 350 +/- 10 degrees C 3 + 0.5/-0 seconds	
	XC5206		XC5XXX
Period	: Oct.	1, 1997 to Oct. 1, 2000	
Combined Started Lot	1		1
Combined Completed Lots:	1		1
Failures:	0		0
Device on test:	3		3
Failure Analysis:			
Note : Solder	cability test applied to all leads		
			{XILINX ®

	Technology: Device Type: Package Type: Assembly: Pre-conditionning Test Condition: Test Duration: Solder Heat Temp.: Test Duration: Rate:	Si-Gate CMOS XC17XXX Microcircuit Group DD8, PLCC-20 AAPI Steam Age 1 hour min. 230 +/- 5 degrees C 3 +/- 1 seconds 1 +/- 0.1 in./sec.	
	XC 1725	6D	XC17XXX
Period	Oct.	1, 1997 to Oct. 1, 2000	
Combined Started Lot	: 2		2
Combined Completed Lots	: 2		2
Failures	: 0		0
Device on test:	: 8		8
Failure Analysis	:		
Note : Solder	ability test applied to the number of l	eads LTPD 10, 22 leads accept on 0	—{{ XILINX [®]

	Tech Devic Packag Ass Pre-conditionning Test Con Test Du Solder Heat Test Du	nology: Si-Gate CMC e Type: XC4XXX M e Type: PQ-160,240, sembly: Anam ndition: Steam Age aration: 1 hour min. Temp.: 230 +/- 5 deg aration: 3 +/-1 second Rate: 1 +/- 0.1 in.se	DS icrocircuit Group VQFP-100, HQFP-304 rees C s c	
	XC4005XL	XC4044XL	XC4013XLA	XC4XXX
Period:		Oct. 1, 1997 to Oct.	1, 2000	
	1	1	2	4
Combined Started Lot:				
Combined Started Lot: ombined Completed Lots:	1	1	2	4
Combined Started Lot: ombined Completed Lots: Failures:	1 0	1 0	2 0	4 0
Combined Started Lot: ombined Completed Lots: Failures: Device on test:	1 0 4	1 0 3	2 0 7	4 0 14

Reliability Testing Summary-Packages Low Temperature Soldering Heat Test

Technology:	Si-Gate CMOS
Device Type:	XC17XXX Microcircuit Group
Package Type:	PLCC-20, DD-8
Steam Age:	2 hours
Flux:	RMA
Solder Heat Temp.:	215 +/- 5 degrees C

XC17256D

XC17XXX

Period:	Oct. 1, 1997 to Oct. 1, 2000	
Combined Started Lot:	2	2
Combined Completed Lots:	2	2
Failures:	0	0
Device on test:	8	8
Failure Analysis:		
Note : Solderability test app	lied to the number of leads LTPD 10, 22 leads accept	on 0 \$* XII INX_
		₹、 ∧ILIN∧-

Reliability Testing Summary-Packages Low Temperature Soldering Heat Test								
	Technol Device T Package T Steam A F Solder Heat Ter	QFP-100						
	XC4005XL	XC4044XL	XC4013XLA	XC4XXX				
Period:		Oct. 1, 1997 to Oct. 1	, 2000					
Combined Started Lot:	2	1	2	5				
Combined Completed Lots:	2	1	2	5				
Failures:	0	0	0	0				
Device on test:	7	3	6	16				
Failure Analysis:								
Note : Solderabilit	ty test applied to the num	ber of leads LTPD 10, 2	22 leads accept on 0					
				_\$`` XII INX®				

Board Level Reliability Test

FG676, FG680, FG860, & FG1156

2nd Level Reliability Test Xilinx FG676, FG680, FG860, &FG1156

Package Details

Package	Size	I/O	Pitch	Ball Size	Pad Opening	Pad Type	Die Size	Substrate
FG860 (SBGA)	42.5x42.5	860	1.0	0.6	0.48	SMD	22.45x21.44x0.3	0.98 Thk, 3 Layer
FG1156 (PBGA)	35x35	1156	1.0	0.6	0.48	SMD	23.11x21.13x0.3	0.56 Thk, 4 Layer
FG676 (PBGA)	27x27	676	1.0	0.6	0.48	SMD	17.8x17.8x0.3	0.56 Thk, 4 Layer
FG680 (SBGA)	40x40	680	1.0	0.6	0.48	SMD	20.3x20.3x0.3	0.98 Thk, 3 Layer

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All Dimensions in mm

Motherboard Design & Assembly Details

- 4 Layer, FR-4, 1.6mm Thick, OSP Finish
- 0.38mm Pad Diameter/0.53mm Solder Mask Opening (NSMD Pads)
- 0.20mm SS Laser Cut Stencil, 0.43mm Aperture Opening, No Clean Paste

Test Conditions

- TC1 : -40<>125°C, 15 minutes ramps,15 minutes dwells, 1 cycle/hour
- TC2 : -55<>125°C, 3 minutes ramps, 12 minutes dwells, 2 cycles/hour
- TC3: 0 <>100°C, 10 minutes ramps, 5 minutes dwells, 2 cycles/hour

Failure Criteria

- Continuous Scanning of Daisy Chain Nets (Every 2 minutes)
- Threshold Resistance: 500 ohms
- OPEN: An Event with Resistance of Net > Threshold Resistance
- FAIL: At Least 2 OPENs within a Temperature Cycle
- Log 15 FAILURES for each Net

2nd Level Reliability Test Xilinx FG676, FG680, FG860, &FG1156

Summary of Test Results

Package	Test Condition	Cycles Completed	# Tested	# Failed	1st Failure (cycles)	Mean Life (cycles)
FG676	TC1	2112	32	27	1341	1830
FG676	TC2	2126	32	26	1434	1788
FG676	TC3	7029	32	4	5909*	N/A
FG680	TC1	5222	29	20	4219	4796
FG680	TC2	3960	32	16	2883	3891
FG680	TC3	6790	32	0	N/A	N/A
FG860	TC3	5044	32	0	N/A	N/A
FG1156	TC1	3108	32	30	1601	2386
FG1156	TC2	2507	48	32	1666	2256
FG1156	TC3	5044	32	0	N/A	N/A

* First failure

- All Packages Passed at least 1000 cycles of TC1 & TC2 Conditions
- TC2 is more Damaging than TC1 for FG680 (Heat Slug Package), No Significant Difference for FG676 & FG1156 (PBGA Type Packages)

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2nd Level Reliability Test - FG676 (PBGA)

Package



2nd Level Reliability Test - FG680 (SBGA)

Package



2nd Level Reliability Test - FG1156 (PBGA)

Package



2nd Level Reliability Test - FG860 (SBGA)

Package

Package	Size	I/O	Pitch	Ball Size	Pad Opening	Pad Type	Die Size	Substrate
FG860 (SBGA)	42.5x42.5	860	1.0	0.6	0.48	SMD	22.45x21.44x0.3	0.98 Thk, 3 Layer

All Dimensions in mm

Motherboard

- 1.6mm Thick
- 0.38mm Pad NSMD

Package	Test Condition	Cycles Completed	# Tested	# Failed	1st Failure (cycles)	Mean Life (cycles)
FG860	TC3	5044	32	0	N/A	N/A

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Test Data

- TC3 Only
- 5044 Cycles Completed
- No Failures